



ISO5852S High-CMTI 2.5-A / 5-A Isolated IGBT, MOSFET Gate Driver with Split Outputs and Active Safety Features

1 Features

- 100-kV/ μ s Minimum Common-Mode Transient Immunity (CMTI) at $V_{CM} = 1500$ V
- Split Outputs to Provide 2.5-A Peak Source and 5-A Peak Sink Currents
- Short Propagation Delay: 76 ns (Typ), 110 ns (Max)
- 2-A Active Miller Clamp
- Output Short-Circuit Clamp
- Soft Turn-Off (STO) during Short Circuit
- Fault Alarm upon Desaturation Detection is Signaled on \overline{FLT} and Reset Through \overline{RST}
- Input and Output Under Voltage Lock-Out (UVLO) with Ready (RDY) Pin Indication
- Active Output Pull-down and Default Low Outputs with Low Supply or Floating Inputs
- 2.25-V to 5.5-V Input Supply Voltage
- 15-V to 30-V Output Driver Supply Voltage
- CMOS Compatible Inputs
- Rejects Input Pulses and Noise Transients Shorter Than 20 ns
- Operating Temperature: -40°C to 125°C Ambient
- Surge Immunity 12800- V_{PK} (according to IEC 61000-4-5)
- Safety and Regulatory Certifications:
 - 8000- V_{PK} V_{IOTM} and 2121- V_{PK} V_{IORM} Reinforced Isolation per DIN V VDE V 0884-10 (VDE V 0884-10):2006-12
 - 5700- V_{RMS} Isolation for 1 Minute per UL 1577
 - CSA Component Acceptance Notice 5A, IEC 60950-1, IEC 60601-1 and IEC 61010-1 End Equipment Standards
 - CQC Certification per GB4943.1-2011
 - All Certifications are Planned

2 Applications

- Isolated IGBT and MOSFET Drives in
 - Industrial Motor Control Drives
 - Industrial Power Supplies
 - Solar Inverters
 - HEV and EV Power Modules
 - Induction Heating

3 Description

The ISO5852S is a 5.7-kV_{RMS}, reinforced isolated gate driver for IGBTs and MOSFETs with split outputs, OUTH and OUTL, providing 2.5-A source and 5-A sink current. The input side operates from a single 2.25-V to 5.5-V supply. The output side allows for a supply range from minimum 15-V to maximum 30-V. Two complementary CMOS inputs control the output state of the gate driver. The short propagation time of 76 ns assures accurate control of the output stage.

An internal desaturation (DESAT) fault detection recognizes when the IGBT is in an overcurrent condition. Upon a DESAT detect, a Mute logic immediately blocks the output of the isolator and initiates a soft-turn-off procedure which disables, OUTH, and pulls OUTL to low over a time span of 2 μ s. When OUTL reaches 2 V with respect to the most negative supply potential, V_{EE2} , the gate driver output is pulled hard to V_{EE2} potential turning the IGBT immediately off.

When desaturation is active, a fault signal is sent across the isolation barrier pulling the \overline{FLT} output at the input side low and blocking the isolator input. Mute logic is activated through the soft-turn-off period. The \overline{FLT} output condition is latched and can be reset only after RDY goes high, through a low-active pulse at the \overline{RST} input.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
ISO5852S	SOIC (16)	10.30 mm x 7.50 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.

Functional Block Diagram

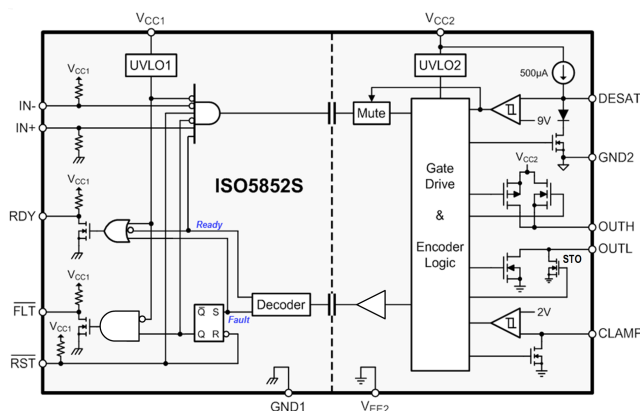


Table of Contents

1 Features	1	9.2 Functional Block Diagram	16
2 Applications	1	9.3 Feature Description	17
3 Description	1	9.4 Device Functional Modes	21
4 Revision History	2	10 Application and Implementation	22
5 Description (continued)	3	10.1 Application Information	22
6 Pin Configuration and Function	3	10.2 Typical Applications	22
7 Specifications	4	11 Power Supply Recommendations	32
7.1 Absolute Maximum Ratings	4	12 Layout	32
7.2 ESD Ratings	4	12.1 Layout Guidelines	32
7.3 Recommended Operating Conditions	4	12.2 PCB Material	32
7.4 Thermal Information	5	12.3 Layout Example	32
7.5 Power Rating	5	13 Device and Documentation Support	33
7.6 Electrical Characteristics	5	13.1 Documentation Support	33
7.7 Switching Characteristics	6	13.2 Community Resources	33
7.8 Typical Characteristics	7	13.3 Trademarks	33
8 Parameter Measurement Information	14	13.4 Electrostatic Discharge Caution	33
9 Detailed Description	16	13.5 Glossary	33
9.1 Overview	16	14 Mechanical, Packaging, and Orderable Information	33

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Original (July 2015) to Revision A	Page
• Moved Features : "100-kV/μs Minimum Common-Mode Transient Immunity.." to the top of the list	1
• Changed from a 1-page Product Preview to the full datasheet.	1
• Changed text "single 3-V To: 5.5-V supply" to "single 2.25-V to 5.5-V supply" in the Description	1
• Changed text "IGBT is in an overload condition" To: "IGBT is in an overcurrent condition" in the Description	1
• Changed text "and reduces the voltage at OUTL over a minimum time span of 2 μs" To: "and pulls OUTL to low over a time span of 2 μs" in the Description	1
• Changed paragraph 3 of the Description	1
• Changed the Functional Block Diagram , added STO on pin OUTL	1

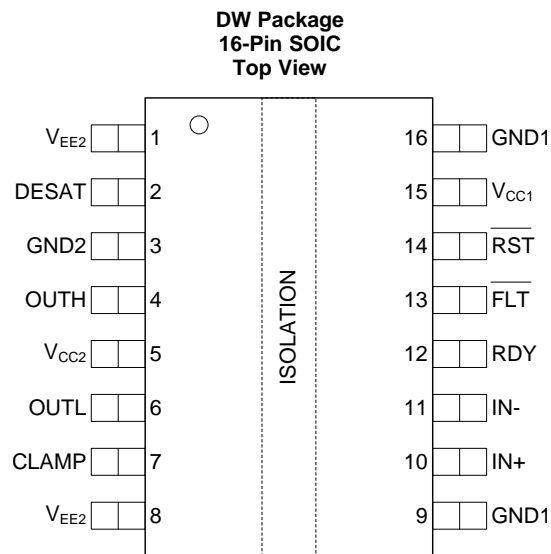
5 Description (continued)

When the IGBT is turned off during normal operation with bipolar output supply, the output is hard clamp to V_{EE2} . If the output supply is unipolar, an active Miller clamp can be used, allowing Miller current to sink across a low impedance path preventing IGBT to be dynamically turned on during high voltage transient conditions.

The readiness for the gate driver to be operated is under the control of two undervoltage-lockout circuits monitoring the input side and output side supplies. If either side has insufficient supply the RDY output goes low, otherwise this output is high.

The ISO5852S is available in a 16-pin SOIC package. Device operation is specified over a temperature range from -40°C to 125°C ambient.

6 Pin Configuration and Function



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
V_{EE2}	1, 8	-	Output negative supply. Connect to GND2 for Unipolar supply application.
DESAT	2	I	Desaturation voltage input
GND2	3	-	Gate drive common. Connect to IGBT emitter.
OUTH	4	O	Positive gate drive voltage output
V_{CC2}	5	-	Most positive output supply potential.
OUTL	6	O	Negative gate drive voltage output
CLAMP	7	O	Miller clamp output
GND1	9, 16	-	Input ground
IN+	10	I	Non-inverting gate drive voltage control input
IN-	11	I	Inverting gate drive voltage control input
RDY	12	O	Power-good output, active high when both supplies are good.
$\overline{\text{FLT}}$	13	O	Fault output, low-active during DESAT condition
$\overline{\text{RST}}$	14	I	Reset input, apply a low pulse to reset fault latch.
V_{CC1}	15	-	Positive input supply (2.25-V to 5.5-V)

7 Specifications

7.1 Absolute Maximum Ratings⁽¹⁾

Over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC1}	Supply voltage input side		GND1 - 0.3	6	V
V _{CC2}	Positive supply voltage output side	(V _{CC2} – GND2)	–0.3	35	V
V _{EE2}	Negative supply voltage output side	(V _{EE2} – GND2)	–17.5	0.3	V
V _(SUP2)	Total supply output voltage	(V _{CC2} - V _{EE2})	–0.3	35	V
V _(OUTH)	Positive gate driver output voltage		V _{EE2} - 0.3	V _{CC2} + 0.3	V
V _(OUTL)	Negative gate driver output voltage		V _{EE2} - 0.3	V _{CC2} + 0.3	V
I _(OUTH)	Gate driver high output current	Gate driver high output current (max pulse width = 10 μs, max duty cycle = 0.2%)	2.7		A
I _(OUTL)	Gate driver low output current		5.5		A
V _(LIP)	Voltage at IN+, IN-, $\overline{\text{FLT}}$, RDY, $\overline{\text{RST}}$		GND1 - 0.3	V _{CC1} + 0.3	V
I _(LOP)	Output current of $\overline{\text{FLT}}$, RDY		10		mA
V _(DESAT)	Voltage at DESAT		GND2 - 0.3	V _{CC2} + 0.3	V
V _(CLAMP)	Clamp voltage		V _{EE2} - 0.3	V _{CC2} + 0.3	V
T _J	Junction temperature		–40	150	°C
T _{STG}	Storage temperature		–65	150	°C

- (1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability

7.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{CC1}	Supply voltage input side	2.25		5.5	V
V _{CC2}	Positive supply voltage output side (V _{CC2} – GND2)	15		30	V
V _(EE2)	Negative supply voltage output side (V _{EE2} – GND2)	–15		0	V
V _(SUP2)	Total supply voltage output side (V _{CC2} – V _{EE2})	15		30	V
V _(IH)	High-level input voltage (IN+, IN-, $\overline{\text{RST}}$)	0.7 x V _{CC1}		V _{CC1}	V
V _(IL)	Low-level input voltage (IN+, IN-, $\overline{\text{RST}}$)	0		0.3 x V _{CC1}	V
t _{UI}	Pulse width at IN+, IN- for full output (C _{LOAD} = 1 nF)	40			ns
t _{RST}	Pulse width at $\overline{\text{RST}}$ for resetting fault latch	800			ns
T _A	Ambient temperature	–40		125	°C

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		DW (SOIC)	UNIT
		16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	99.6	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	48.5	
R _{θJB}	Junction-to-board thermal resistance	56.5	
Ψ _{JT}	Junction-to-top characterization parameter	29.2	
Ψ _{JB}	Junction-to-board characterization parameter	56.5	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, [SPRA953](#).

7.5 Power Rating

			VALUE	UNIT
P _D	Maximum power dissipation ⁽¹⁾	V _{CC1} = 5.5-V, V _{CC2} = 30-V, T _A = 25°C	1255	mW
P _{ID}	Maximum Input power dissipation	V _{CC1} = 5.5-V, V _{CC2} = 30-V, T _A = 25°C	175	
P _{OD}	Maximum Output power dissipation	V _{CC1} = 5.5-V, V _{CC2} = 30-V, T _A = 25°C	1080	

(1) Full chip power dissipation is de-rated 10.04 mW/°C beyond 25°C ambient temperature. At 125°C ambient temperature, a maximum of 251 mW total power dissipation is allowed. Power dissipation can be optimized depending on ambient temperature and board design, while ensuring that Junction temperature does not exceed 150°C.

7.6 Electrical Characteristics

Over recommended operating conditions unless otherwise noted. All typical values are at T_A = 25°C, V_{CC1} = 5 V, V_{CC2} – GND2 = 15 V, GND2 – V_{EE2} = 8 V

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VOLTAGE SUPPLY					
V _{IT+(UVLO1)}	Positive-going UVLO1 threshold voltage input side			2.25	V
V _{IT-(UVLO1)}	Negative-going UVLO1 threshold voltage input side	1.7			V
V _{HYS(UVLO1)}	UVLO1 Hysteresis voltage (V _{IT+} – V _{IT-}) input side		0.2		V
V _{IT+(UVLO2)}	Positive-going UVLO2 threshold voltage output side		12	13	V
V _{IT-(UVLO2)}	Negative-going UVLO2 threshold voltage output side	9.5	11		V
V _{HYS(UVLO2)}	UVLO2 Hysteresis voltage (V _{IT+} – V _{IT-}) output side		1		V
I _{Q1}	Input supply quiescent current		2.8	4.5	mA
I _{Q2}	Output supply quiescent current		3.6	6	mA
LOGIC I/O					
V _{IT+(IN,RST)}	Positive-going input threshold voltage (IN+, IN-, RST)		0.7 × V _{CC1}		V
V _{IT-(IN,RST)}	Negative-going input threshold voltage (IN+, IN-, RST)	0.3 × V _{CC1}			V
V _{HYS(IN,RST)}	Input hysteresis voltage (IN+, IN-, RST)		0.15 × V _{CC1}		V
I _{IH}	High-level input leakage at (IN+) ⁽¹⁾	IN+ = V _{CC1}	100		μA
I _{IL}	Low-level input leakage at (IN-, RST) ⁽²⁾	IN- = GND1, RST = GND1	-100		μA
I _{PU}	Pull-up current of $\overline{\text{FLT}}$, RDY	V _(RDY) = GND1, V _(FLT) = GND1	100		μA
V _(OL)	Low-level output voltage at $\overline{\text{FLT}}$, RDY	I _(FLT) = 5 mA		0.2	V
GATE DRIVER STAGE					
V _(OUTPD)	Active output pull-down voltage	I _(OUTH/L) = 200 mA, V _{CC2} = open		2	V
V _{OUTH}	High-level output voltage	I _(OUTH) = -20 mA	V _{CC2} - 0.5	V _{CC2} - 0.24	V
V _{OUTL}	Low-level output voltage	I _(OUTL) = 20 mA		V _{EE2} + 13	V _{EE2} + 50
I _(OUTH)	High-level output peak current	IN+ = high, IN- = low, V _(OUTH) = V _{CC2} - 15 V	1.5	2.5	A

(1) I_{IH} for IN-, $\overline{\text{RST}}$ pin is zero as they are pulled high internally

(2) I_{IL} for IN+ is zero, as it is pulled low internally

Electrical Characteristics (continued)

Over recommended operating conditions unless otherwise noted. All typical values are at $T_A = 25^\circ\text{C}$, $V_{CC1} = 5\text{ V}$, $V_{CC2} = \text{GND2} = 15\text{ V}$, $\text{GND2} - V_{EE2} = 8\text{ V}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$I_{(OUTL)}$ Low-level output peak current	$\text{IN+} = \text{low}$, $\text{IN-} = \text{high}$, $V_{(OUTL)} = V_{EE2} + 15\text{ V}$	3.4	5		A
$I_{(OLF)}$ Low level output current during fault condition			130		mA
ACTIVE MILLER CLAMP					
$V_{(CLP)}$ Low-level clamp voltage	$I_{(CLP)} = 20\text{ mA}$		$V_{EE2} + 0.015$	$V_{EE2} + 0.08$	V
$I_{(CLP)}$ Low-level clamp current	$V_{(CLAMP)} = V_{EE2} + 2.5\text{ V}$	1.6	2.5	3.3	A
$V_{(CLTH)}$ Clamp threshold voltage		1.6	2.1	2.5	V
SHORT CIRCUIT CLAMPING					
$V_{(CLP-OUTH)}$ Clamping voltage ($V_{OUTH} - V_{CC2}$)	$\text{IN+} = \text{high}$, $\text{IN-} = \text{low}$, $t_{CLP} = 10\text{ }\mu\text{s}$, $I_{(OUTH)} = 500\text{ mA}$		1.1	1.3	V
$V_{(CLP-OUTL)}$ Clamping voltage ($V_{OUTL} - V_{CC2}$)	$\text{IN+} = \text{high}$, $\text{IN-} = \text{low}$, $t_{CLP} = 10\text{ }\mu\text{s}$, $I_{(OUTL)} = 500\text{ mA}$		1.3	1.5	V
$V_{(CLP-CLAMP)}$	Clamping voltage ($V_{CLP} - V_{CC2}$)		1.3		V
	Clamping voltage at CLAMP	$\text{IN+} = \text{High}$, $\text{IN-} = \text{Low}$, $I_{(CLP)} = 20\text{ mA}$	0.7	1.1	V
$V_{(CLP-OUTL)}$ Clamping voltage at OUTL ($V_{CLP} - V_{CC2}$)	$\text{IN+} = \text{High}$, $\text{IN-} = \text{Low}$, $I_{(OUTL)} = 20\text{ mA}$		0.7	1.1	V
DESAT PROTECTION					
$I_{(CHG)}$ Blanking capacitor charge current	$V_{(DESAT)} - \text{GND2} = 2\text{ V}$	0.42	0.5	0.58	mA
$I_{(DCHG)}$ Blanking capacitor discharge current	$V_{(DESAT)} - \text{GND2} = 6\text{ V}$	9	14		mA
$V_{(DSTH)}$ DESAT threshold voltage with respect to GND2		8.3	9	9.5	V
$V_{(DSL)}$ DESAT voltage with respect to GND2, when OUTH/L is driven low		0.4		1	V

7.7 Switching Characteristics

Over recommended operating conditions unless otherwise noted. All typical values are at $T_A = 25^\circ\text{C}$, $V_{CC1} = 5\text{ V}$, $V_{CC2} = \text{GND2} = 15\text{ V}$, $\text{GND2} - V_{EE2} = 8\text{ V}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_r Output signal rise time at OUTH	$C_{LOAD} = 1\text{ nF}$ see Figure 41, Figure 42, and Figure 43	12	18	35	ns
t_f Output signal fall time at OUTL		12	20	37	ns
t_{PLH} , t_{PHL} Propagation Delay			76	110	ns
t_{sk-p} Pulse Skew $ t_{PHL} - t_{PLH} $				20	ns
t_{sk-pp} Part-to-part skew				30 ⁽¹⁾	ns
$t_{GF}(\text{IN}/\text{RST})$ Glitch filter on IN+ , IN- , $\overline{\text{RST}}$		20	30	40	ns
$t_{DS}(90\%)$ DESAT sense to 90% $V_{OUTH/L}$ delay	$C_{LOAD} = 10\text{ nF}$		553	760	ns
$t_{DS}(10\%)$ DESAT sense to 10% $V_{OUTH/L}$ delay			2	3.5	μs
$t_{DS}(\text{GF})$ DESAT glitch filter delay	$C_{LOAD} = 1\text{ nF}$		330		ns
$t_{DS}(\text{FLT})$ DESAT sense to $\overline{\text{FLT}}$ -low delay	see Figure 43			1.4	μs
t_{LEB} Leading edge blanking time	see Figure 41 and Figure 42	310	400	480	ns
$t_{GF}(\text{RSTFLT})$ Glitch filter on $\overline{\text{RST}}$ for resetting FLT		300		800	ns
C_I Input capacitance ⁽²⁾	$V_I = V_{CC1}/2 + 0.4 \times \sin(2\pi ft)$, $f = 1\text{ MHz}$, $V_{CC1} = 5\text{ V}$		2		pF
CMTI Common-mode transient immunity	$V_{CM} = 1500\text{ V}$, see Figure 44	100	120		kV/ μs

(1) Measured at same supply voltage and temperature condition

(2) Measured from input pin to ground.

7.8 Typical Characteristics

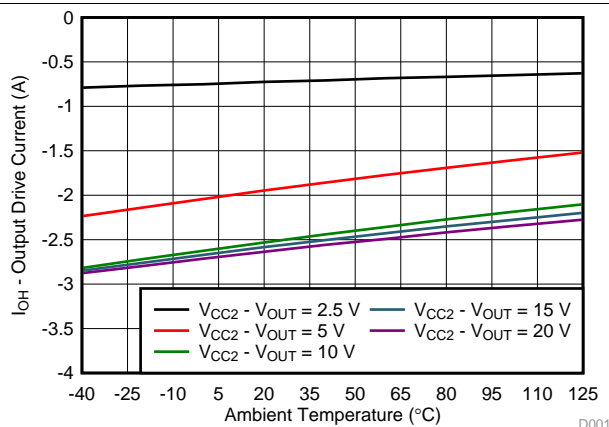


Figure 1. Output High Drive Current vs Temperature

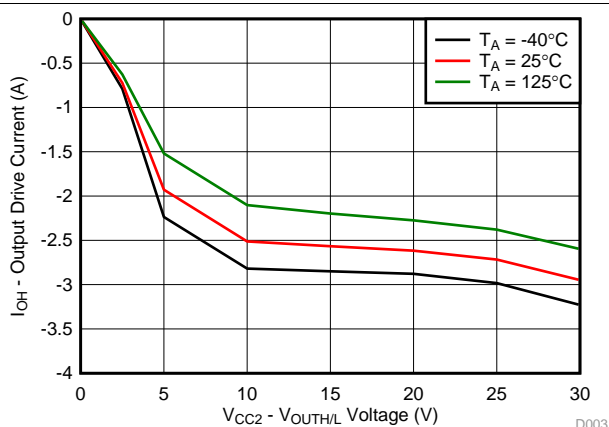


Figure 2. Output High Drive Current vs Output Voltage

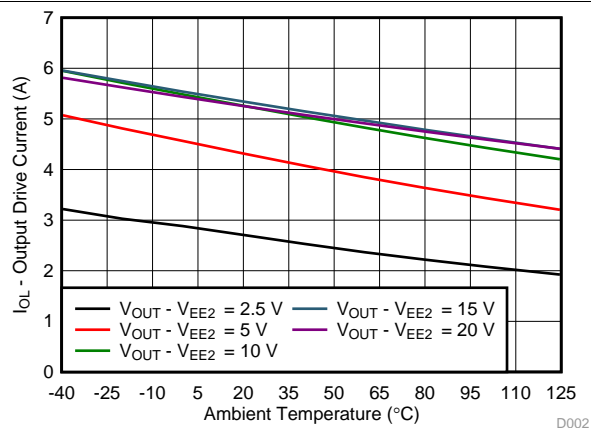


Figure 3. Output Low Drive Current vs Temperature

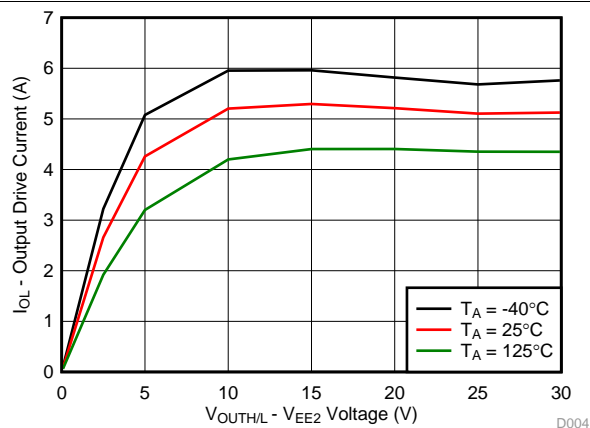


Figure 4. Output Low Drive Current vs Output Voltage

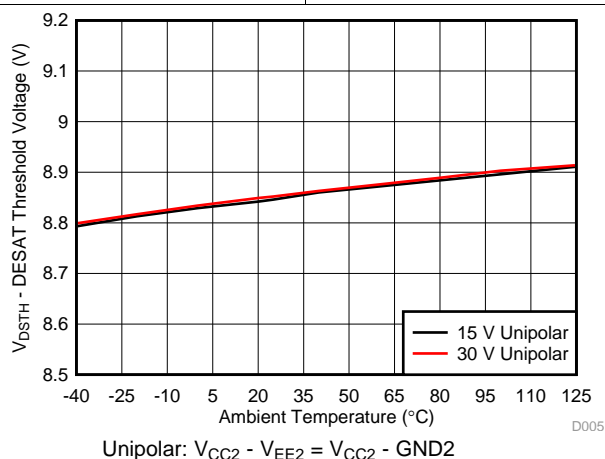
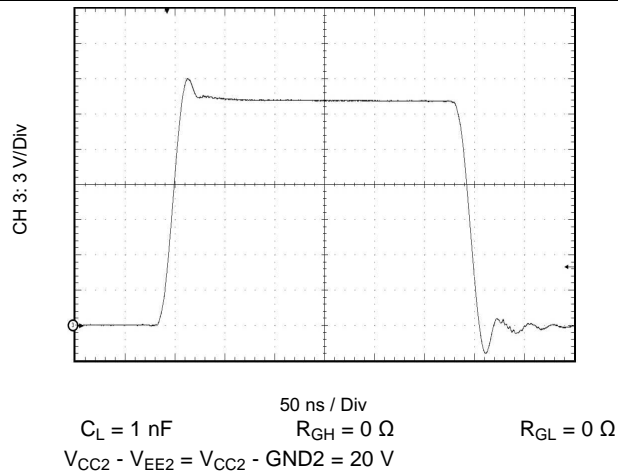
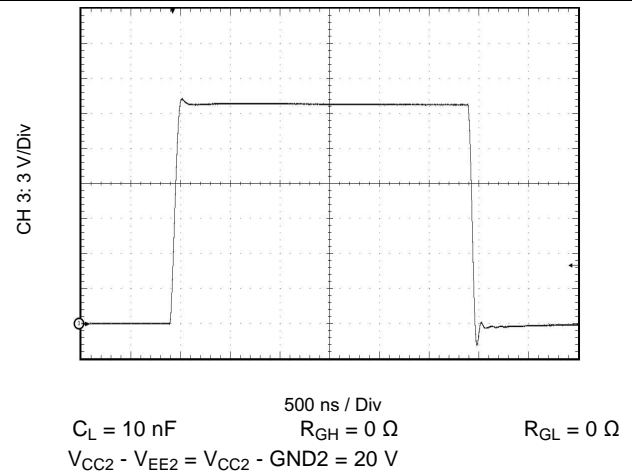
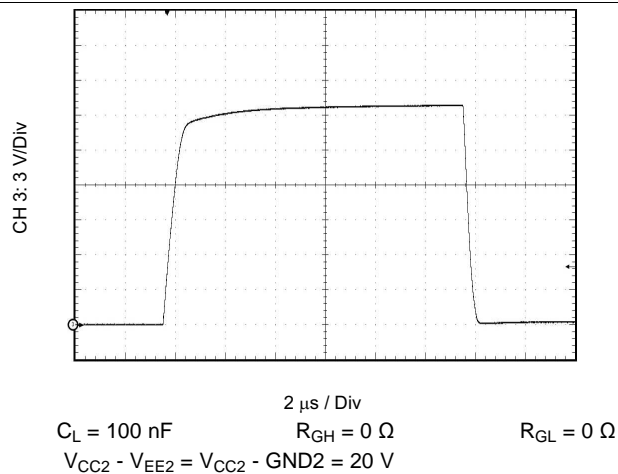
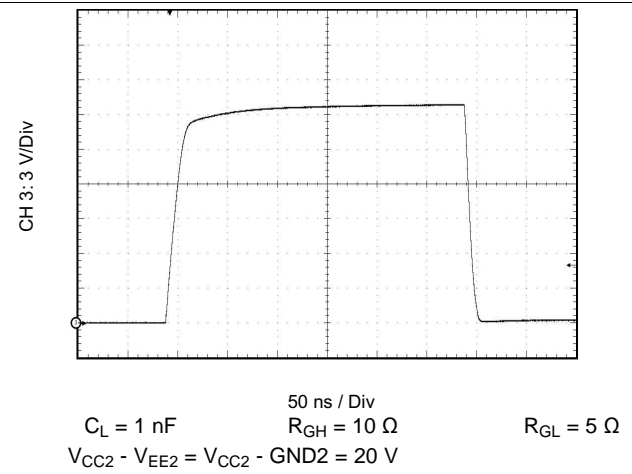
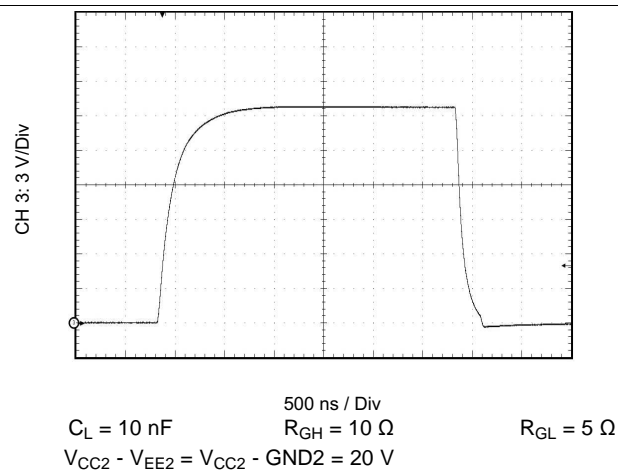
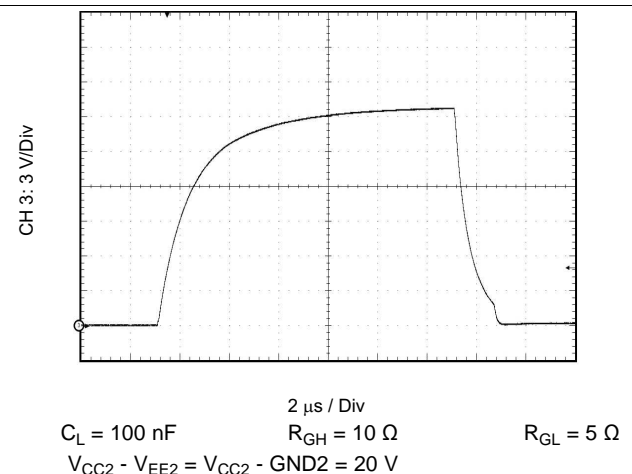
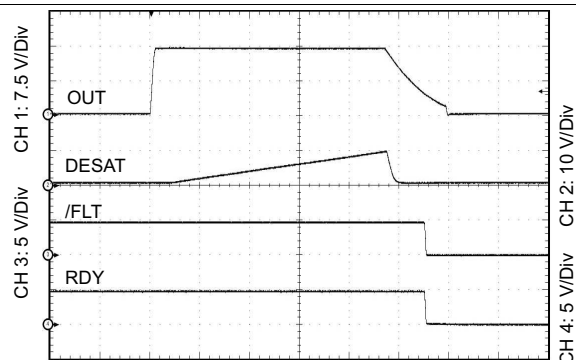


Figure 5. DESAT Threshold Voltage vs Temperature

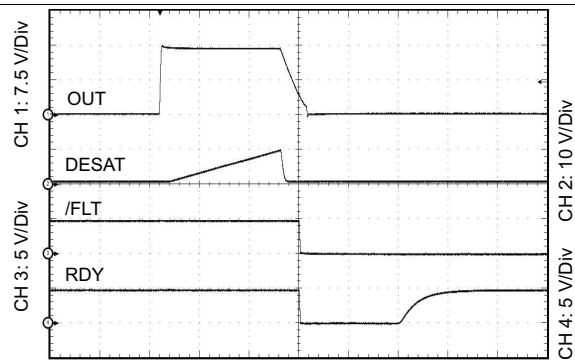
Typical Characteristics (continued)

Figure 6. Output Transient Waveform

Figure 7. Output Transient Waveform

Figure 8. Output Transient Waveform

Figure 9. Output Transient Waveform

Figure 10. Output Transient Waveform

Figure 11. Output Transient Waveform

Typical Characteristics (continued)



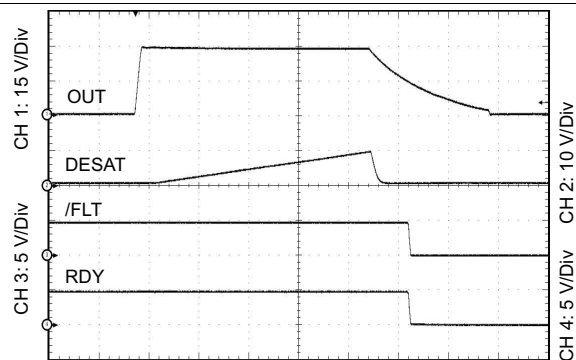
1 μ s / Div
 $C_L = 10$ nF $R_{GH} = 0$ Ω $R_{GL} = 0$ Ω
 $V_{CC2} - V_{EE2} = V_{CC2} - GND2 = 15$ V $DESAT = 220$ pF

Figure 12. Output Transient Waveform DESAT, RDY and FLT



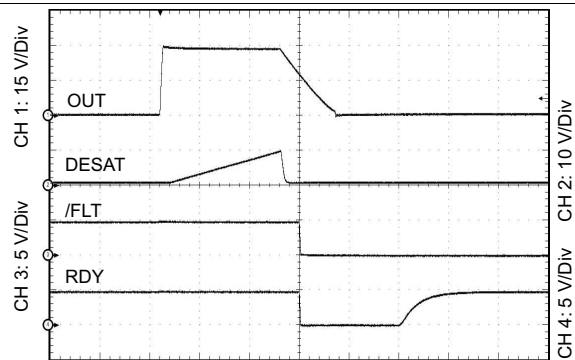
2 μ s / Div
 $C_L = 10$ nF $R_{GH} = 0$ Ω $R_{GL} = 0$ Ω
 $V_{CC2} - V_{EE2} = V_{CC2} - GND2 = 15$ V $DESAT = 220$ pF

Figure 13. Output Transient Waveform DESAT, RDY and FLT



1 μ s / Div
 $C_L = 10$ nF $R_{GH} = 0$ Ω $R_{GL} = 0$ Ω
 $V_{CC2} - V_{EE2} = V_{CC2} - GND2 = 30$ V $DESAT = 220$ pF

Figure 14. Output Transient Waveform DESAT, RDY and FLT



2 μ s / Div
 $C_L = 10$ nF $R_{GH} = 0$ Ω $R_{GL} = 0$ Ω
 $V_{CC2} - V_{EE2} = V_{CC2} - GND2 = 30$ V $DESAT = 220$ pF

Figure 15. Output Transient Waveform DESAT, RDY and FLT

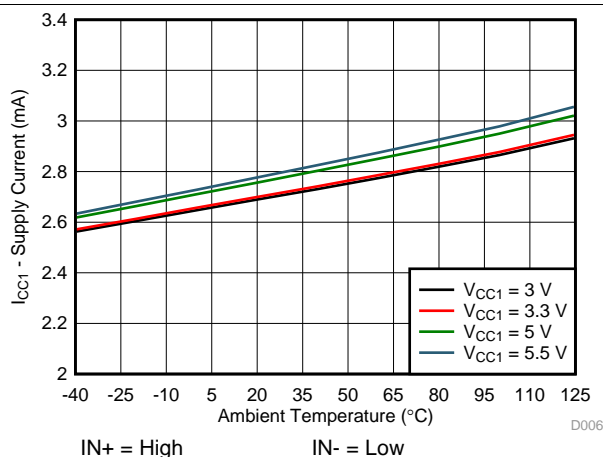


Figure 16. I_{CC1} Supply Current vs Temperature

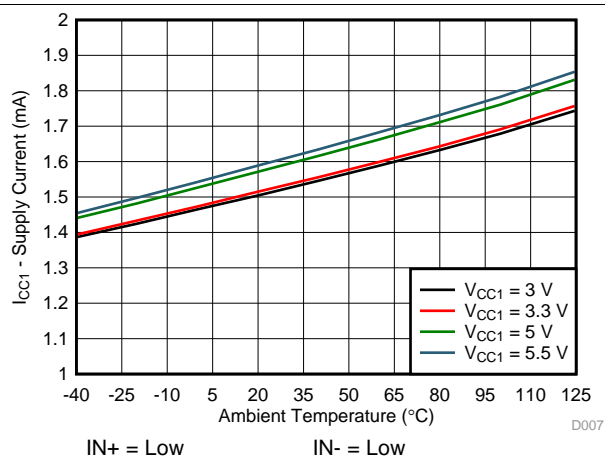


Figure 17. I_{CC1} Supply Current vs Temperature

Typical Characteristics (continued)

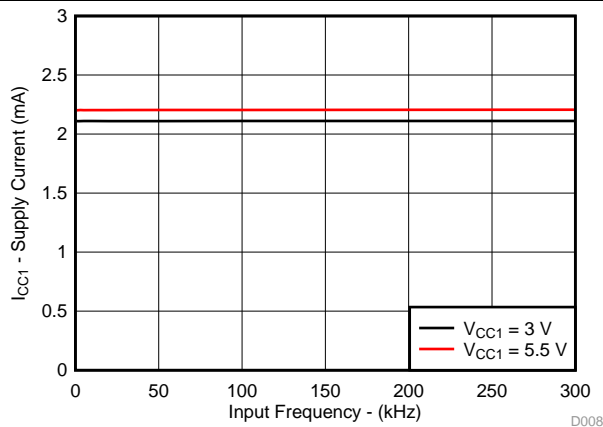
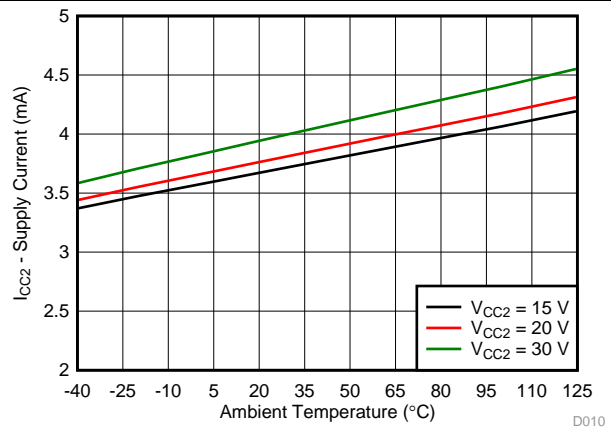


Figure 18. I_{CC1} Supply Current vs Input Frequency



Input frequency = 1 kHz

Figure 19. I_{CC2} Supply Current vs Temperature

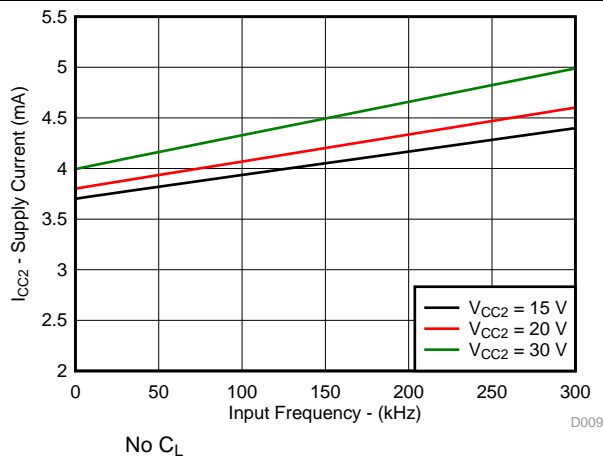


Figure 20. I_{CC2} Supply Current vs Input Frequency

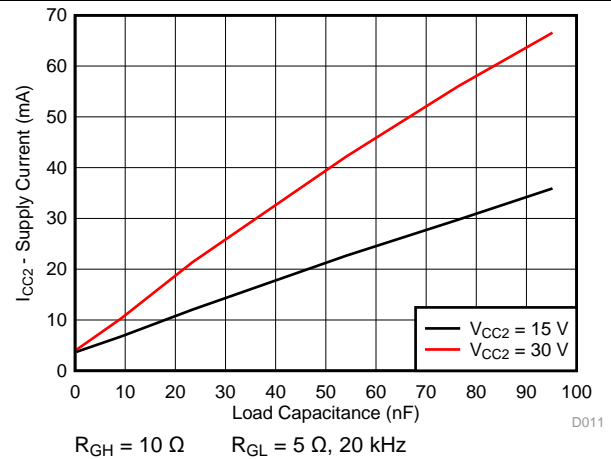


Figure 21. I_{CC2} Supply Current vs Load Capacitance

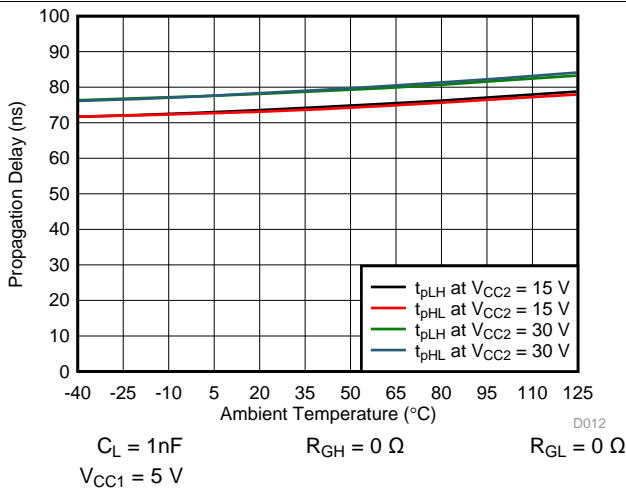


Figure 22. Propagation Delay vs Temperature

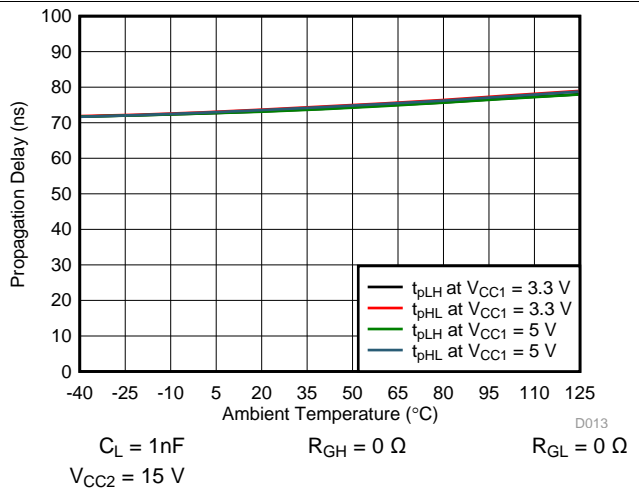


Figure 23. Propagation Delay vs Temperature

Typical Characteristics (continued)

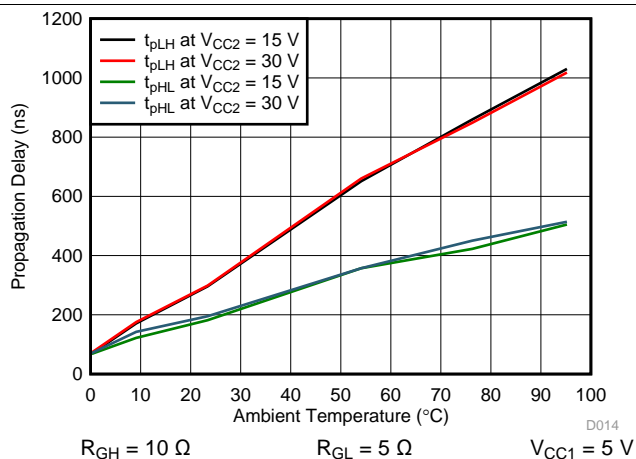


Figure 24. Propagation Delay vs Load Capacitance

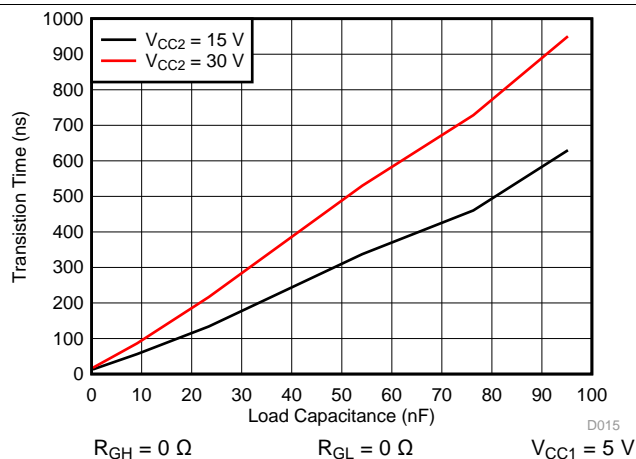


Figure 25. t_r Rise Time vs Load Capacitance

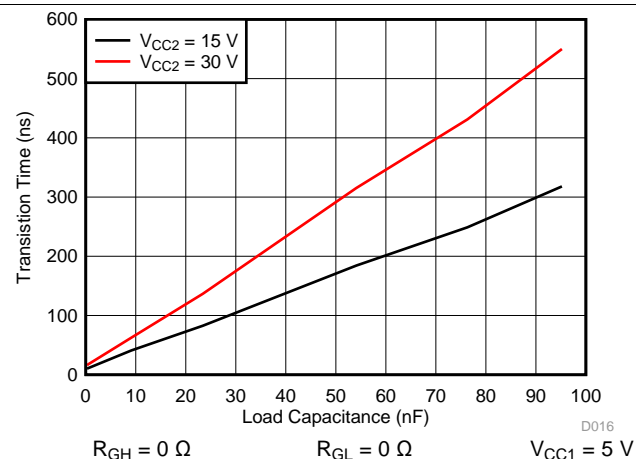


Figure 26. t_f Fall Time v. Load Capacitance

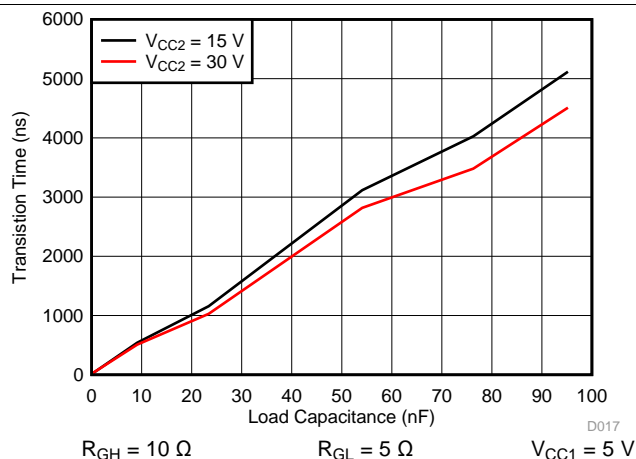


Figure 27. t_r Rise Time vs Load Capacitance

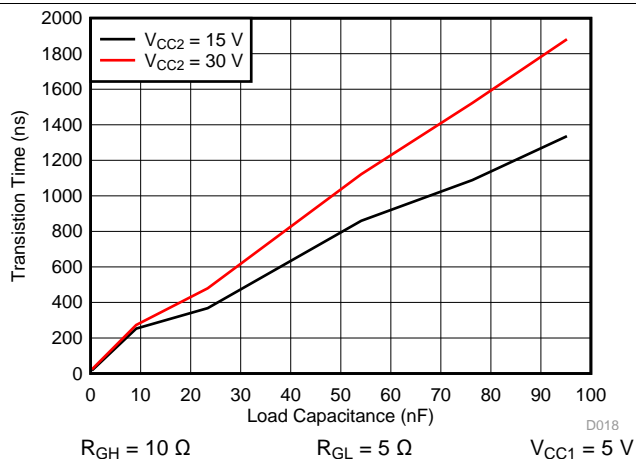


Figure 28. t_f Fall Time vs Load Capacitance

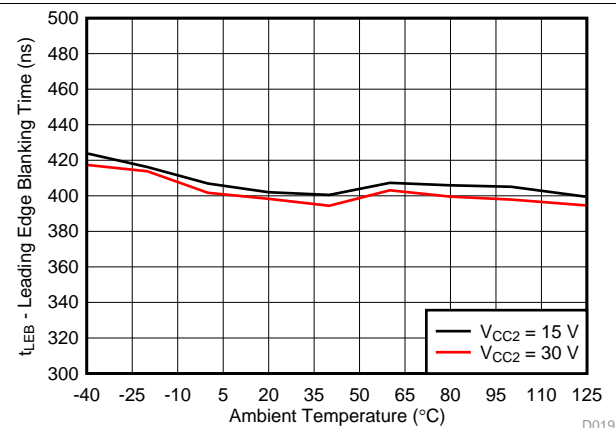


Figure 29. Leading Edge Blanking Time With Temperature

Typical Characteristics (continued)

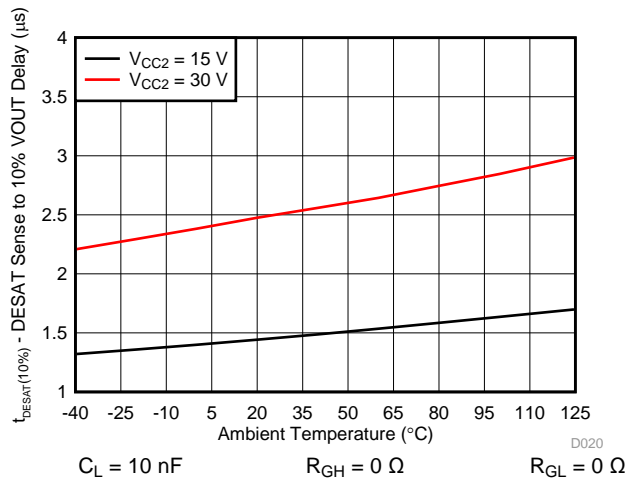


Figure 30. DESAT Sense to VOUT 10% Delay vs Temperature

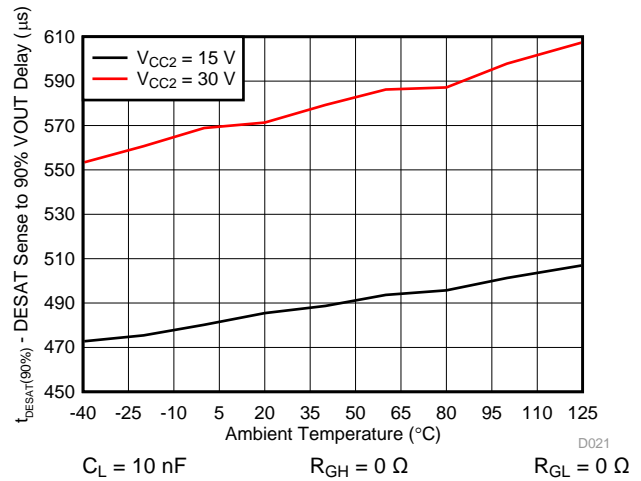


Figure 31. DESAT Sense to VOUT 90% Delay vs Temperature

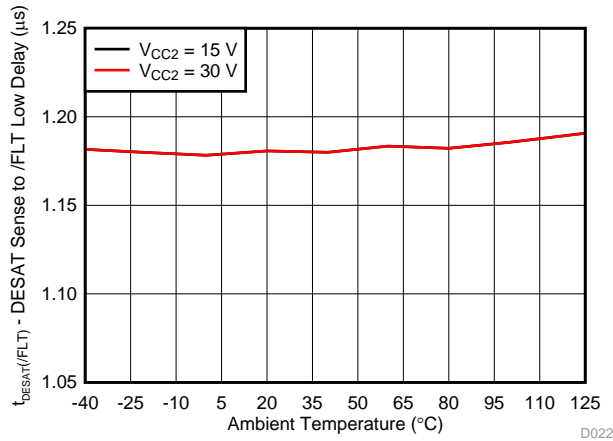


Figure 32. DESAT Sense to Fault Low Delay vs Temperature

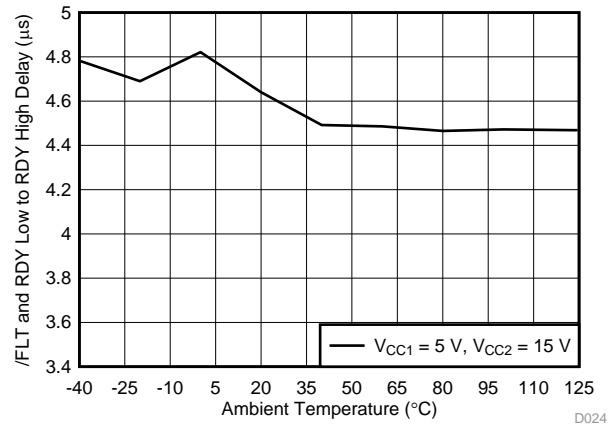


Figure 33. Fault and RDY Low to RDY High Delay vs Temperature

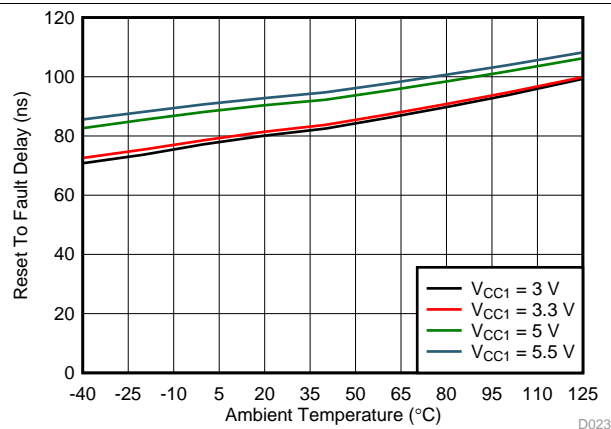


Figure 34. Reset to Fault Delay Across Temperature

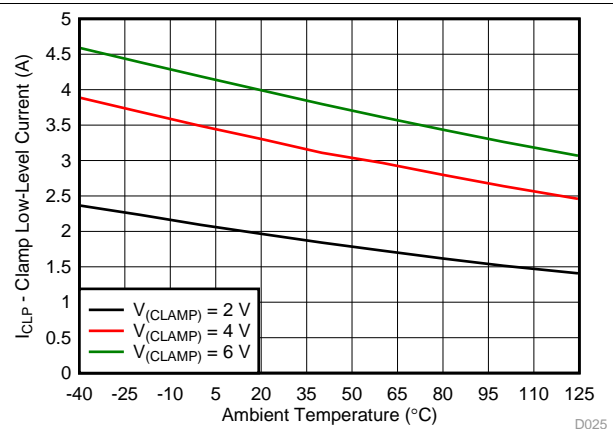


Figure 35. Miller Clamp Current vs Temperature

Typical Characteristics (continued)

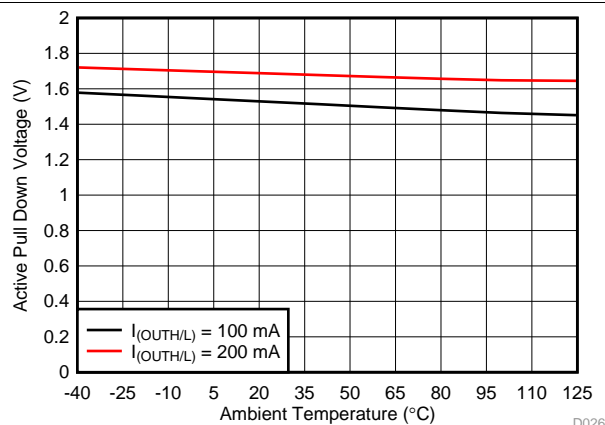


Figure 36. Active Pull Down Voltage vs Temperature

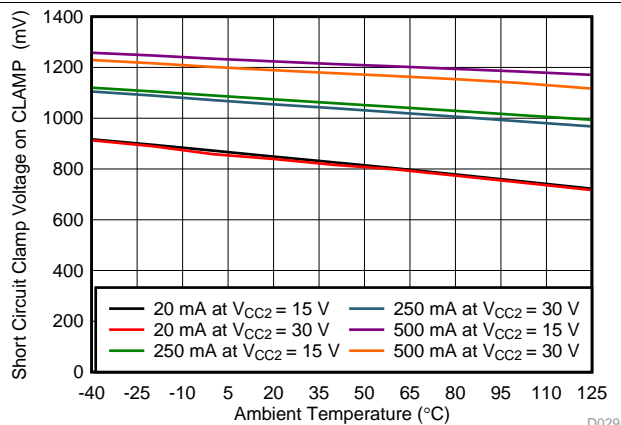


Figure 37. Short Circuit Clamp Voltage on Clamp Across Temperature

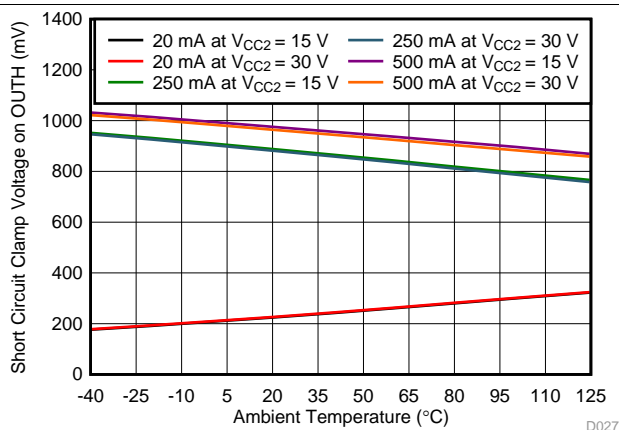


Figure 38. Short Circuit Clamp Voltage on OUTH Across Temperature

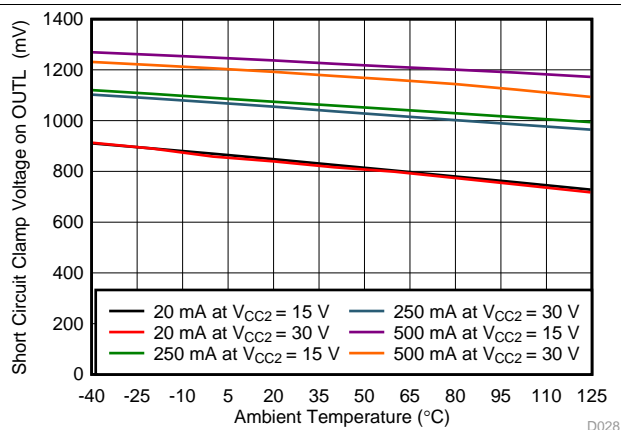


Figure 39. Short Circuit Clamp Voltage on OUTL Across Temperature

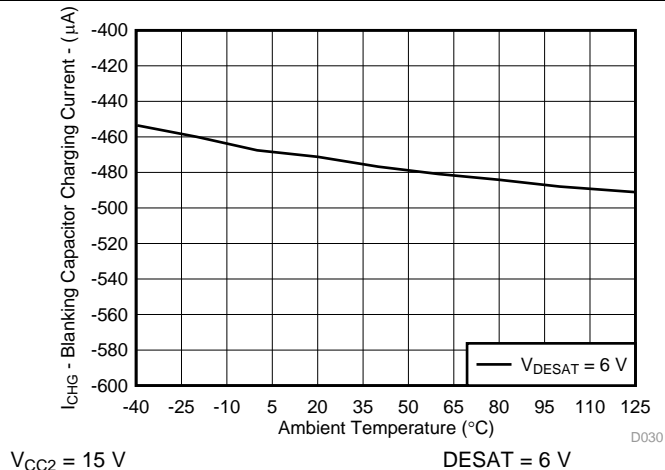


Figure 40. Blanking Capacitor Charging Current vs Temperature

8 Parameter Measurement Information

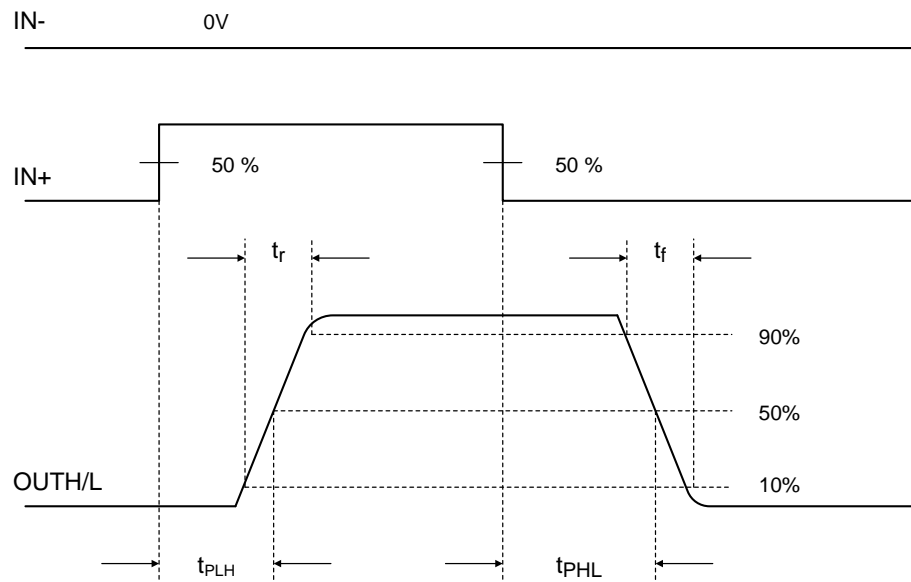


Figure 41. OUTH/L Propagation Delay, Non-Inverting Configuration

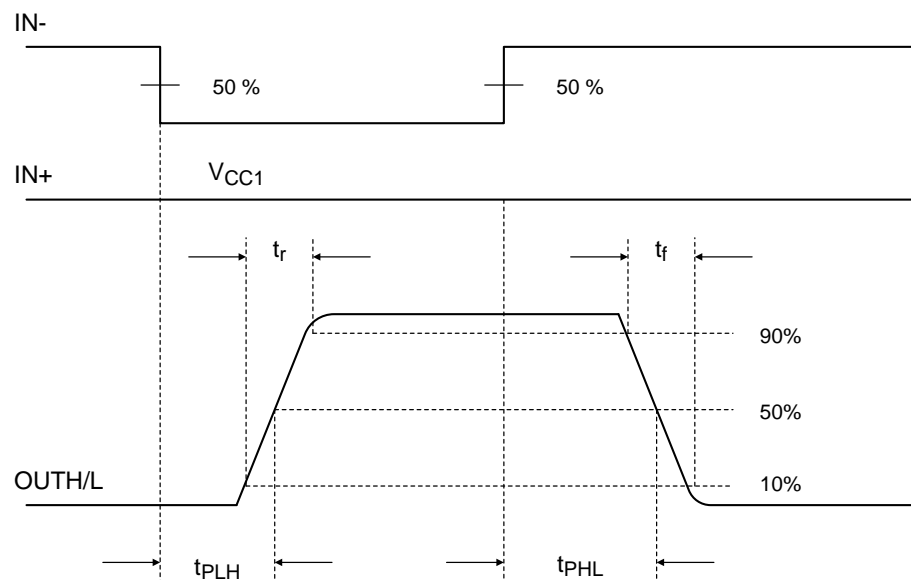


Figure 42. OUTH/L Propagation Delay, Inverting Configuration

Parameter Measurement Information (continued)

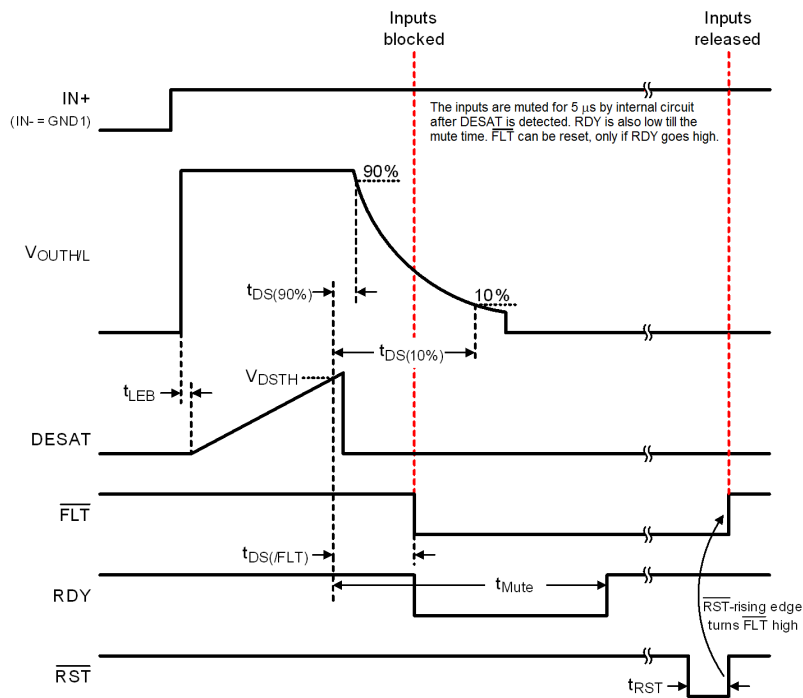


Figure 43. DESAT, OUTH/L, $\overline{\text{FLT}}$, $\overline{\text{RST}}$ Delay

ISO5852S

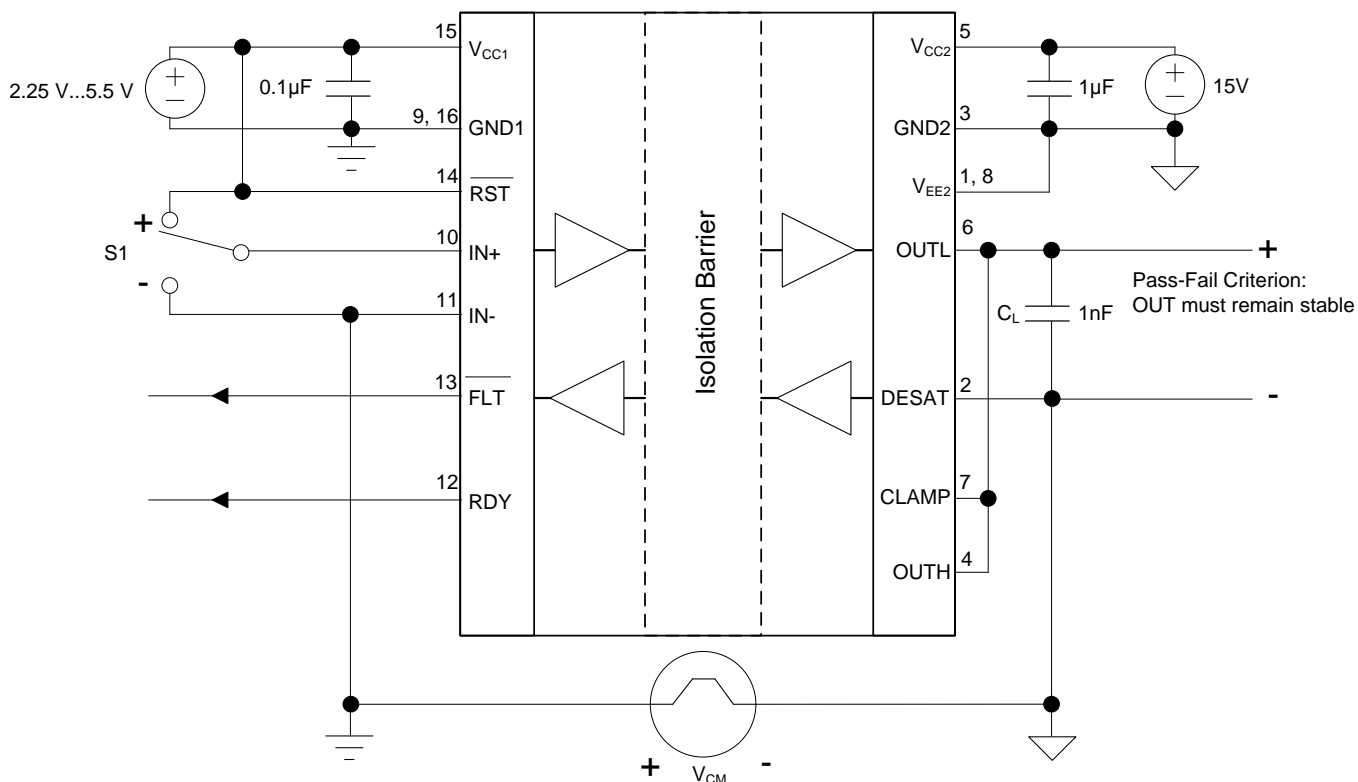


Figure 44. Common-Mode Transient Immunity Test Circuit

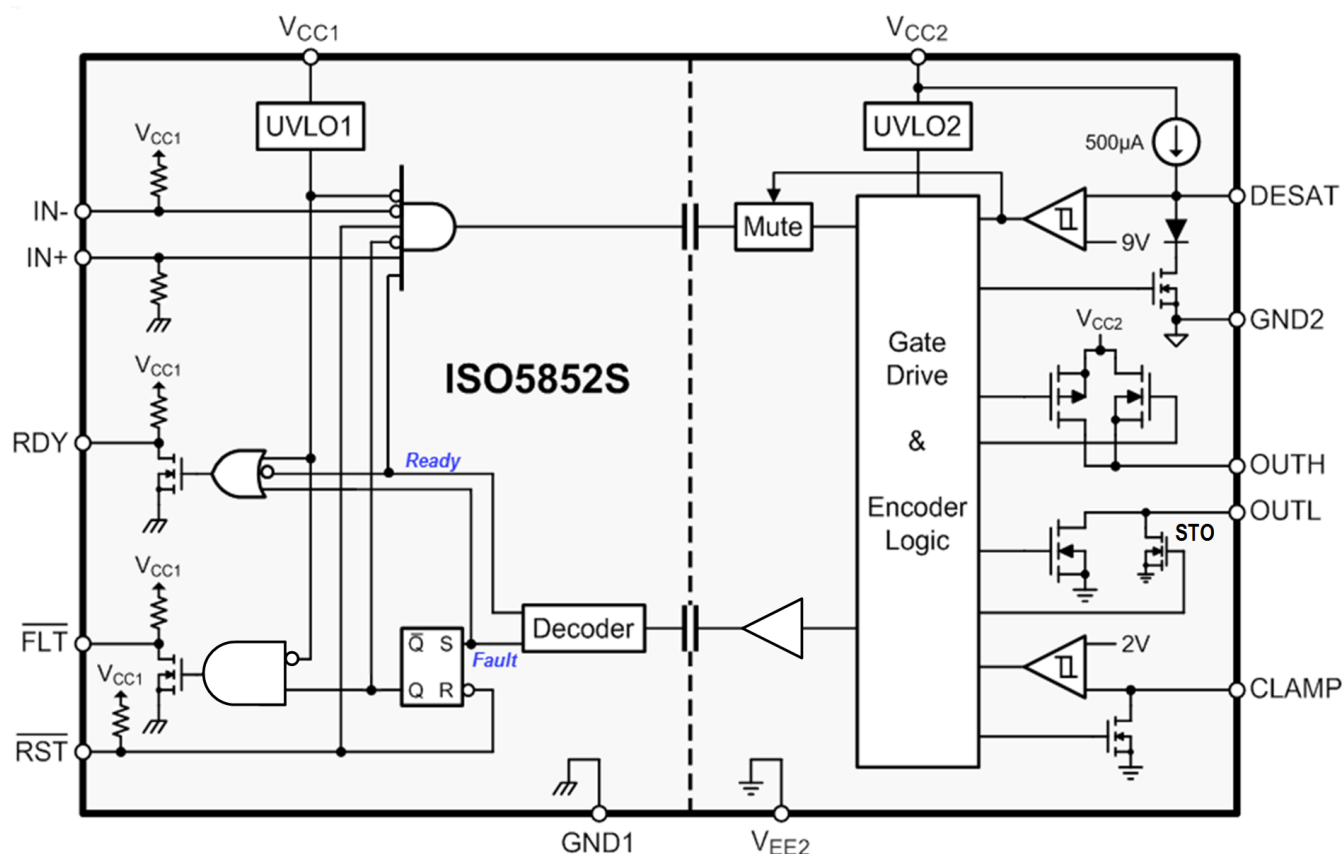
9 Detailed Description

9.1 Overview

The ISO5852S is an isolated gate driver for IGBTs and MOSFETs. Input CMOS logic and output power stage are separated by a Silicon dioxide (SiO_2) capacitive isolation.

The IO circuitry on the input side interfaces with a micro controller and consists of gate drive control and RESET ($\overline{\text{RST}}$) inputs, READY (RDY) and FAULT ($\overline{\text{FLT}}$) alarm outputs. The power stage consists of power transistors to supply 2.5-A pull-up and 5-A pull-down currents to drive the capacitive load of the external power transistors, as well as DESAT detection circuitry to monitor IGBT collector-emitter overvoltage under short circuit events. The capacitive isolation core consists of transmit circuitry to couple signals across the capacitive isolation barrier, and receive circuitry to convert the resulting low-swing signals into CMOS levels. The ISO5852S also contains under voltage lockout circuitry to prevent insufficient gate drive to the external IGBT, and active output pull-down feature which ensures that the gate-driver output is held low, if the output supply voltage is absent. The ISO5852S also has an active Miller clamp which can be used to prevent parasitic turn-on of the external power transistor, due to Miller effect, for unipolar supply operation.

9.2 Functional Block Diagram



9.3 Feature Description

9.3.1 Supply and active Miller clamp

The ISO5852S supports both bipolar and unipolar power supply with active Miller clamp.

For operation with bipolar supplies, the IGBT is turned off with a negative voltage on its gate with respect to its emitter. This prevents the IGBT from unintentionally turning on because of current induced from its collector to its gate due to Miller effect. In this condition it is not necessary to connect CLAMP output of the gate driver to the IGBT gate. Typical values of V_{CC2} and V_{EE2} for bipolar operation are 15-V and -8-V with respect to GND2.

For operation with unipolar supply, typically, V_{CC2} is connected to 15-V with respect to GND2, and V_{EE2} is connected to GND2. In this use case, the IGBT can turn-on due to additional charge from IGBT Miller capacitance caused by a high voltage slew rate transition on the IGBT collector. To prevent IGBT to turn on, the CLAMP pin is connected to IGBT gate and Miller current is sunk through a low impedance CLAMP transistor.

Miller CLAMP is designed for Miller current up to 2-A. When the IGBT is turned-off and the gate voltage transitions below 2-V the CLAMP current output is activated.

9.3.2 Active Output Pull-down

The Active output pull-down feature ensures that the IGBT gate OUTH/L is clamped to V_{EE2} to ensure safe IGBT off-state, when the output side is not connected to the power supply.

9.3.3 Undervoltage Lockout (UVLO) with Ready (RDY) Pin Indication Output

Undervoltage Lockout (UVLO) ensures correct switching of IGBT. The IGBT is turned-off, if the supply V_{CC1} drops below $V_{IT-(UVLO1)}$, irrespective of IN+, IN- and RST input till V_{CC1} goes above $V_{IT+(UVLO1)}$.

In similar manner, the IGBT is turned-off, if the supply V_{CC2} drops below $V_{IT-(UVLO2)}$, irrespective of IN+, IN- and RST input till V_{CC2} goes above $V_{IT+(UVLO2)}$.

Ready (RDY) pin indicates status of input and output side Under Voltage Lock-Out (UVLO) internal protection feature. If either side of device have insufficient supply (V_{CC1} or V_{CC2}), the RDY pin output goes low; otherwise, RDY pin output is high. RDY pin also serves as an indication to the micro-controller that the device is ready for operation.

9.3.4 Soft Turn-Off, Fault (\overline{FLT}) and Reset (\overline{RST})

During IGBT overcurrent condition, a Mute logic initiates a soft-turn-off procedure which disables, OUTH, and pulls OUTL to low over a time span of 2 μ s. When desaturation is active, a fault signal is sent across the isolation barrier pulling the \overline{FLT} output at the input side low and blocking the isolator input. Mute logic is activated through the soft-turn-off period. The \overline{FLT} output condition is latched and can be reset only after RDY goes high, through a low-active pulse at the \overline{RST} input. \overline{RST} has an internal filter to reject noise and glitches. By asserting \overline{RST} for at least the specified minimum duration (800ns), device input logic can be enabled or disabled.

9.3.5 Short Circuit Clamp

Under short circuit events it is possible that currents are induced back into the gate-driver OUTH/L and CLAMP pins due to parasitic Miller capacitance between the IGBT collector and gate terminals. Internal protection diodes on OUTH/L and CLAMP help to sink these currents while clamping the voltages on these pins to values slightly higher than the output side supply.

Feature Description (continued)

9.3.6 High Voltage Feature Description

9.3.6.1 Package Insulation and Safety-Related Specifications

over recommended operating conditions (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(I01) Minimum air gap (clearance)	Shortest terminal-to-terminal distance through air	8			mm
L(I02) ⁽¹⁾ Minimum external tracking (creepage)	Shortest terminal-to-terminal distance across the package surface	8			mm
CTI Tracking resistance (comparative tracking index)	DIN EN 60112 (VDE 0303-11); IEC 60112; Material Group I according to IEC 60664-1; UL 746A	600			V

(1) Per JEDEC package dimensions.

NOTE

Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance.

Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.

9.3.6.2 Insulation Characteristics

PARAMETER	TEST CONDITIONS	SPECIFICATION	UNIT
DTI Distance through the insulation	Minimum internal gap (internal clearance)	21	μm
V _{IOWM} Maximum isolation working voltage	Time dependent dielectric breakdown (TDDb) Test	1500	V _{RMS}
		2121	V _{DC}
DIN V VDE V 0884-10 (VDE V 0884-10):2006-12			
V _{IORM} Maximum repetitive peak isolation voltage		2121	V _{PK}
V _{PR} Input to output test voltage	Method A, After Input/Output safety test subgroup 2/3, V _{PR} = 1.2 × V _{IORM} , t = 10 sec, Partial discharge < 5 pC	2545	
	Method A, After environmental tests subgroup 1, V _{PR} = 1.6 × V _{IORM} , t = 10 sec (qualification) Partial discharge < 5 pC	3393	
	Method B1, 100% Production test, V _{PR} = 1.875 × V _{IORM} , t = 1 sec Partial discharge < 5 pC	3976	
V _{IOTM} Maximum Transient isolation voltage	V _{TEST} = V _{IOTM} , t = 60 sec (qualification), t = 1 sec (100% production)	8000	
V _{IOSM} Maximum surge isolation voltage	Test method per IEC 60065, 1.2/50 μs waveform, V _{TEST} = 1.6 × V _{IOSM} = 12800 V _{PK} (qualification) ⁽¹⁾	8000	
R _S Insulation resistance	V _{IO} = 500 V at T _S	> 10 ⁹	Ω
R _{IO} Isolation resistance, input to output ⁽²⁾	V _{IO} = 500 V, T _A = 25°C	> 10 ¹²	Ω
	V _{IO} = 500 V, 100°C ≤ T _A ≤ max	> 10 ¹¹	Ω
C _{IO} Barrier capacitance, input to output ⁽²⁾	V _{IO} = 0.4 × sin(2πft), f = 1 MHz	1	pF
Pollution degree		2	
UL 1577			
V _{ISO} Withstanding Isolation voltage	V _{TEST} = V _{ISO} , t = 60 sec (qualification), V _{TEST} = 1.2 × V _{ISO} = 6840 V _{RMS} , t = 1 sec (100% production)	5700	V _{RMS}

(1) Testing is carried out in air or oil to determine the intrinsic surge immunity of the isolation barrier.

(2) All pins on each side of the barrier tied together creating a two-terminal device

9.3.6.3 Regulatory Information

VDE	CSA	UL	CQC
Plan to certify according to DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 and DIN EN 60950-1 (VDE 0805 Teil 1):2011-01	Plan to certify under CSA Component Acceptance Notice 5A, IEC 60950-1, IEC 61010-1, and IEC 60601-1	Plan to certify under 1577 Component Recognition Program	Plan to certify according to GB 4943.1-2011
Reinforced Insulation Maximum Transient isolation voltage, 8000 V _{PK} ; Maximum surge isolation voltage, 8000 V _{PK} ; Maximum repetitive peak isolation voltage, 2121 V _{PK}	Isolation Rating of 5700 V _{RMS} ; Reinforced insulation per CSA 61010-1-12 and IEC 61010-1 (3rd Ed.), 300 V _{RMS} max working voltage); Reinforced insulation per CSA 60950-1-07+A1+A2 and IEC 60950-1 (2nd Ed.), 800 V _{RMS} max working voltage (pollution degree 2, material group I) ; 2 MOPP (Means of Patient Protection) per CSA 60601-1:14 and IEC 60601-1 Ed. 3.1, 250 V _{RMS} (354 V _{PK}) max working voltage	Single Protection, 5700 V _{RMS} ⁽¹⁾	Reinforced Insulation, Altitude ≤ 5000m, Tropical climate, 250 V _{RMS} maximum working voltage
Certification planned	Certification planned	Certification planned	Certification planned

(1) Production tested ≥ 6840 V_{RMS} for 1 second in accordance with UL 1577.

9.3.6.4 IEC 60664-1 Rating Table

PARAMETER	TEST CONDITIONS	SPECIFICATION
Basic Isolation Group	Material Group	I
Installation Classification	Rated Mains Voltage ≤ 600 V _{RMS}	I-IV
	Rated Mains Voltage ≤ 1000 V _{RMS}	I-III

9.3.6.5 Safety Limiting Values

Safety limiting intends to prevent potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier, potentially leading to secondary system failures.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_S Safety input, output or supply current	$\theta_{JA} = 99.6^{\circ}\text{C/W}$, $V_I = 2.75\text{ V}$, $T_J = 150^{\circ}\text{C}$, $T_A = 25^{\circ}\text{C}$			456	mA
	$\theta_{JA} = 99.6^{\circ}\text{C/W}$, $V_I = 3.6\text{ V}$, $T_J = 150^{\circ}\text{C}$, $T_A = 25^{\circ}\text{C}$			346	
	$\theta_{JA} = 99.6^{\circ}\text{C/W}$, $V_I = 5.5\text{ V}$, $T_J = 150^{\circ}\text{C}$, $T_A = 25^{\circ}\text{C}$			228	
	$\theta_{JA} = 99.6^{\circ}\text{C/W}$, $V_I = 15\text{ V}$, $T_J = 150^{\circ}\text{C}$, $T_A = 25^{\circ}\text{C}$			84	
	$\theta_{JA} = 99.6^{\circ}\text{C/W}$, $V_I = 30\text{ V}$, $T_J = 150^{\circ}\text{C}$, $T_A = 25^{\circ}\text{C}$			42	
P_S Safety input, output, or total power	$\theta_{JA} = 99.6^{\circ}\text{C/W}$, $T_J = 150^{\circ}\text{C}$, $T_A = 25^{\circ}\text{C}$			1255 ⁽¹⁾	
T_S Maximum ambient safety temperature				150	$^{\circ}\text{C}$

(1) Input, output, or the sum of input and output power should not exceed this value

The safety-limiting constraint is the absolute-maximum junction temperature specified in the [Absolute Maximum Ratings](#) table. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the [Thermal Information](#) table is that of a device installed in the High-K Test Board for Leaded Surface-Mount Packages. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.

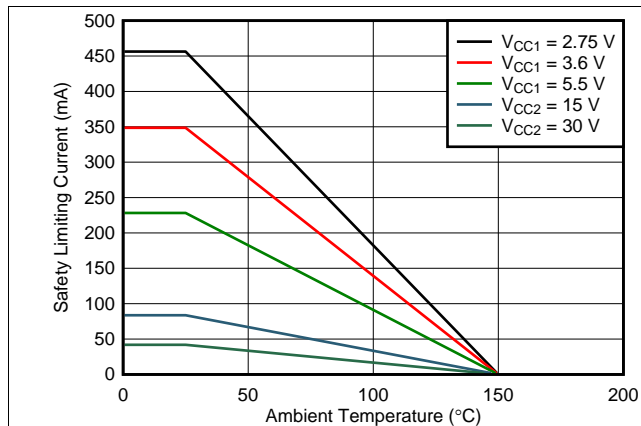


Figure 45. Thermal Derating Curve for Safety Limiting Current per VDE

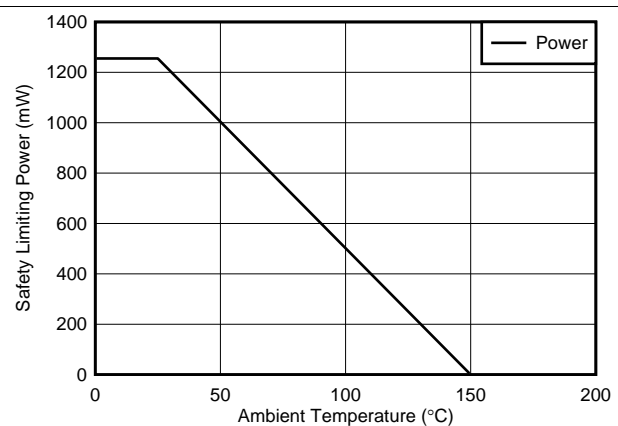


Figure 46. Thermal Derating Curve for Safety Limiting Power per VDE

9.3.6.6 Surge Voltage Rating

			VALUE	UNIT
$V_{(\text{Surge})}$	Surge immunity	1.2/50 μs voltage surge pulse according to IEC 60065 ⁽¹⁾	± 12800	V_{PK}

(1) Testing is carried out in air or oil to determine the intrinsic surge immunity of the isolation barrier.

9.4 Device Functional Modes

In ISO5852S OUTH/L to follow IN+ in normal functional mode, $\overline{\text{FLT}}$ needs to be in high state.

Table 1. Function Table⁽¹⁾

V _{CC1}	V _{CC2}	IN+	IN-	$\overline{\text{RST}}$	RDY	OUTH/L
PU	PD	X	X	X	Low	Low
PD	PU	X	X	X	Low	Low
PU	PU	X	X	Low	High	Low
PU	Open	X	X	X	Low	Low
PU	PU	Low	X	X	High	Low
PU	PU	X	High	X	High	Low
PU	PU	High	Low	High	High	High

(1) PU: Power Up (V_{CC1} ≥ 2.25-V, V_{CC2} ≥ 13-V), PD: Power Down (V_{CC1} ≤ 1.7-V, V_{CC2} ≤ 9.5-V), X: Irrelevant

10 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

The ISO5852S is an isolated gate driver for power semiconductor devices such as IGBTs and MOSFETs. It is intended for use in applications such as motor control, industrial inverters and switched mode power supplies. In these applications, sophisticated PWM control signals are required to turn the power devices on and off, which at the system level eventually may determine, for example, the speed, position, and torque of the motor or the output voltage, frequency and phase of the inverter. These control signals are usually the outputs of a micro controller, and are at low voltage levels such as 2.5 V, 3.3 V or 5 V. The gate controls required by the MOSFETs and IGBTs, on the other hand, are in the range of 30-V (using Unipolar Output Supply) to 15-V (using Bipolar Output Supply), and need high current capability to be able to drive the large capacitive loads offered by those power transistors. Not only that, the gate drive needs to be applied with reference to the Emitter of the IGBT (Source for MOSFET), and by construction, the Emitter node in a gate drive system swings between 0 to the DC bus voltage, that can be several 100s of volts in magnitude.

The ISO5852S is thus used to level shift the incoming 2.5-V, 3.3-V and 5-V control signals from the microcontroller to the 30-V (using Unipolar Output Supply) to 15-V (using Bipolar Output Supply) drive required by the power transistors while ensuring high-voltage isolation between the driver side and the microcontroller side.

10.2 Typical Applications

Figure 47 shows the typical application of a three-phase inverter using six ISO5852S isolated gate drivers. Three-phase inverters are used for variable-frequency drives to control the operating speed of AC motors and for high power applications such as High-Voltage DC (HVDC) power transmission.

The basic three-phase inverter consists of three single-phase inverter switches each comprising two ISO5852S devices that are connected to one of the three load terminals. The operation of the three switches is coordinated so that one switch operates at each 60 degree point of the fundamental output waveform, thus creating a six-step line-to-line output waveform. In this type of applications, carrier-based PWM techniques are applied to retain waveform envelope and cancel harmonics.

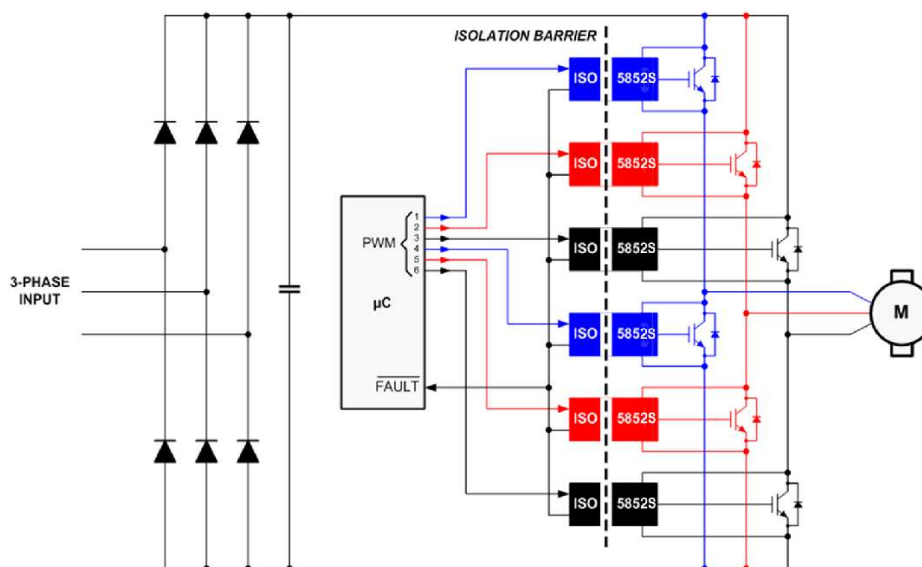


Figure 47. Typical Motor Drive Application

Typical Applications (continued)

10.2.1 Design Requirements

Unlike optocoupler based gate drivers which need external current drivers and biasing circuitry to provide the input control signals, the input control to the ISO5852S is CMOS and can be directly driven by the microcontroller. Other design requirements include decoupling capacitors on the input and output supplies, a pullup resistor on the common drain FLT output signal, and a high-voltage protection diode between the IGBT collector and the DESAT input. Further details are explained in the subsequent sections. Table 2 shows the allowed range for Input and Output supply voltage, and the typical current output available from the gate-driver.

Table 2. Design Parameters

PARAMETER	VALUE
Input supply voltage	2.25-V to 5.5-V
Unipolar output supply voltage ($V_{CC2} - GND2 = V_{CC2} - V_{EE2}$)	15-V to 30-V
Bipolar output supply voltage ($V_{CC2} - V_{EE2}$)	15-V to 30-V
Bipolar output supply voltage ($GND2 - V_{EE2}$)	0-V to 15-V
Output current	2.5-A

10.2.2 Detailed Design Procedure

10.2.2.1 Recommended ISO5852S Application Circuit

The ISO5852S has both, inverting and non-inverting gate control inputs, an active low reset input, and an open drain fault output suitable for wired-OR applications. The recommended application circuit in Figure 48 illustrates a typical gate driver implementation with Unipolar Output Supply and Figure 49 illustrates a typical gate driver implementation with Bipolar Output Supply using the ISO5852S.

A 0.1-μF bypass capacitor, recommended at input supply pin V_{CC1} and 1-μF bypass capacitor, recommended at output supply pin V_{CC2} , provide the large transient currents necessary during a switching transition to ensure reliable operation. The 220 pF blanking capacitor disables DESAT detection during the off-to-on transition of the power device. The DESAT diode (D_{DST}) and its 1-kΩ series resistor are external protection components. The R_G gate resistor limits the gate charge current and indirectly controls the IGBT collector voltage rise and fall times. The open-drain FLT output and RDY output has a passive 10-kΩ pull-up resistor. In this application, the IGBT gate driver is disabled when a fault is detected and will not resume switching until the micro-controller applies a reset signal.

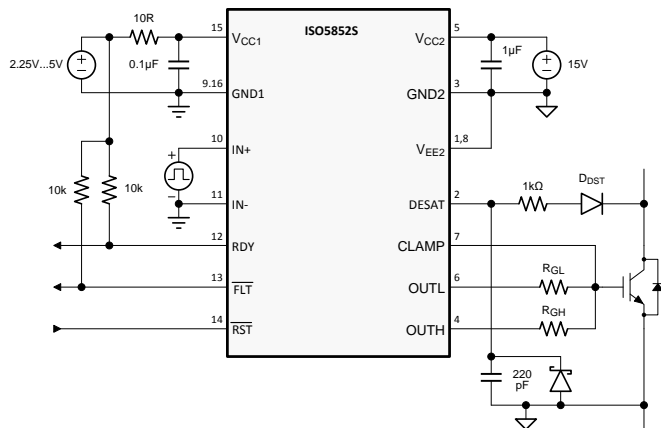


Figure 48. Unipolar Output Supply

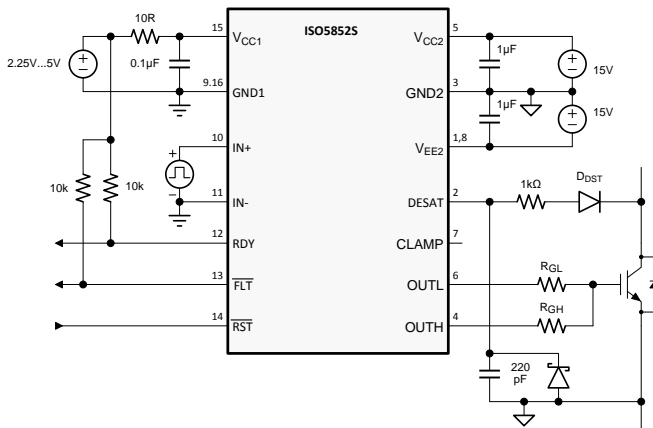


Figure 49. Bipolar Output Supply

10.2.2.2 \overline{FLT} and RDY Pin Circuitry

There is 50-kΩ pull-up resistor internally on \overline{FLT} and RDY pins. The \overline{FLT} and RDY pin is an open-drain output. A 10-kΩ pull-up resistor can be used to make it faster rise and to provide logic high when \overline{FLT} and RDY is inactive, as shown in Figure 50.

Fast common mode transients can inject noise and glitches on $\overline{\text{FLT}}$ and RDY pins due to parasitic coupling. This is dependent on board layout. If required, additional capacitance (100 pF to 300 pF) can be included on the $\overline{\text{FLT}}$ and RDY pins.

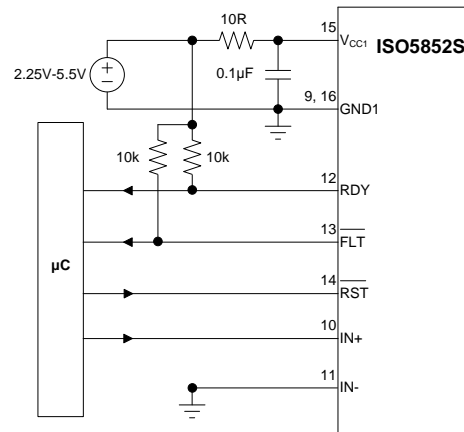


Figure 50. $\overline{\text{FLT}}$ and RDY Pin Circuitry for High CMTI

10.2.2.3 Driving the Control Inputs

The amount of common-mode transient immunity (CMTI) can be curtailed by the capacitive coupling from the high-voltage output circuit to the low-voltage input side of the ISO5852S. For maximum CMTI performance, the digital control inputs, IN+ and IN-, must be actively driven by standard CMOS, push-pull drive circuits. This type of low-impedance signal source provides active drive signals that prevent unwanted switching of the ISO5852S output under extreme common-mode transient conditions. Passive drive circuits, such as open-drain configurations using pull-up resistors, must be avoided. There is a 20 ns glitch filter which can filter a glitch up to 20 ns on IN+ or IN-.

10.2.2.4 Local Shutdown and Reset

In applications with local shutdown and reset, the $\overline{\text{FLT}}$ output of each gate driver is polled separately, and the individual reset lines are asserted low independently to reset the motor controller after a fault condition.

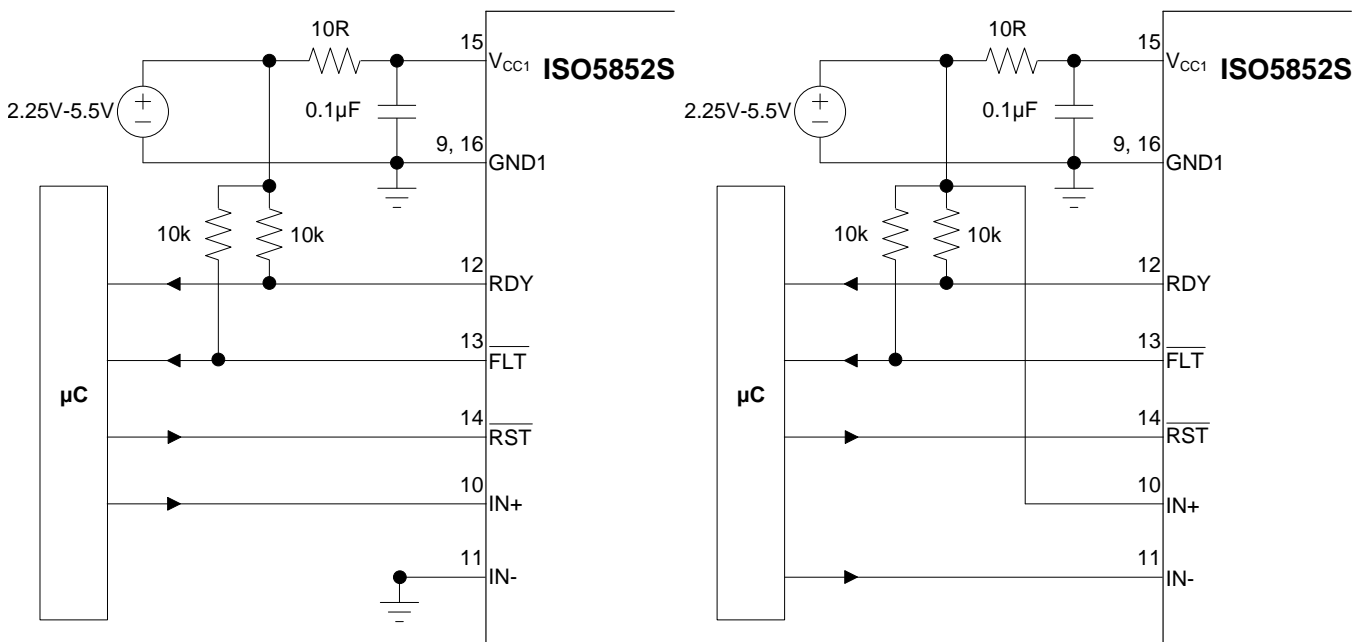


Figure 51. Local Shutdown and Reset for Noninverting (left) and Inverting Input Configuration (right)

10.2.2.5 Global-Shutdown and Reset

When configured for inverting operation, the ISO5852S can be configured to shutdown automatically in the event of a fault condition by tying the $\overline{\text{FLT}}$ output to $\text{IN}+$. For high reliability drives, the open drain $\overline{\text{FLT}}$ outputs of multiple ISO5852S devices can be wired together forming a single, common fault bus for interfacing directly to the micro-controller. When any of the six gate drivers of a three-phase inverter detects a fault, the active low $\overline{\text{FLT}}$ output disables all six gate drivers simultaneously.

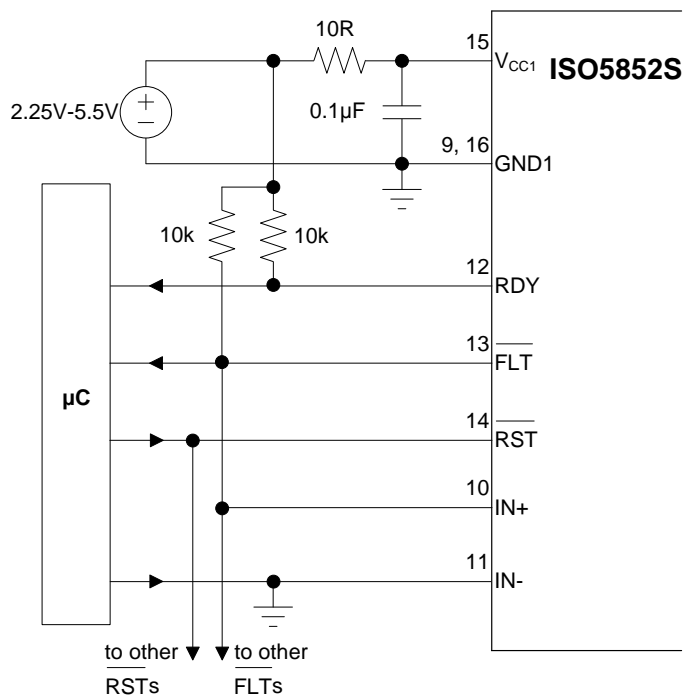


Figure 52. Global Shutdown with Inverting Input Configuration

ISO5852S

SLLSEQ0A – AUGUST 2015 – REVISED SEPTEMBER 2015

www.ti.com

10.2.2.6 Auto-Reset

In this case, the gate control signal at IN+ is also applied to the $\overline{\text{RST}}$ input to reset the fault latch every switching cycle. Incorrect RST makes output go low. A fault condition, however, the gate driver remains in the latched fault state until the gate control signal changes to the 'gate low' state and resets the fault latch.

If the gate control signal is a continuous PWM signal, the fault latch will always be reset before IN+ goes high again. This configuration protects the IGBT on a cycle by cycle basis and automatically resets before the next 'on' cycle.

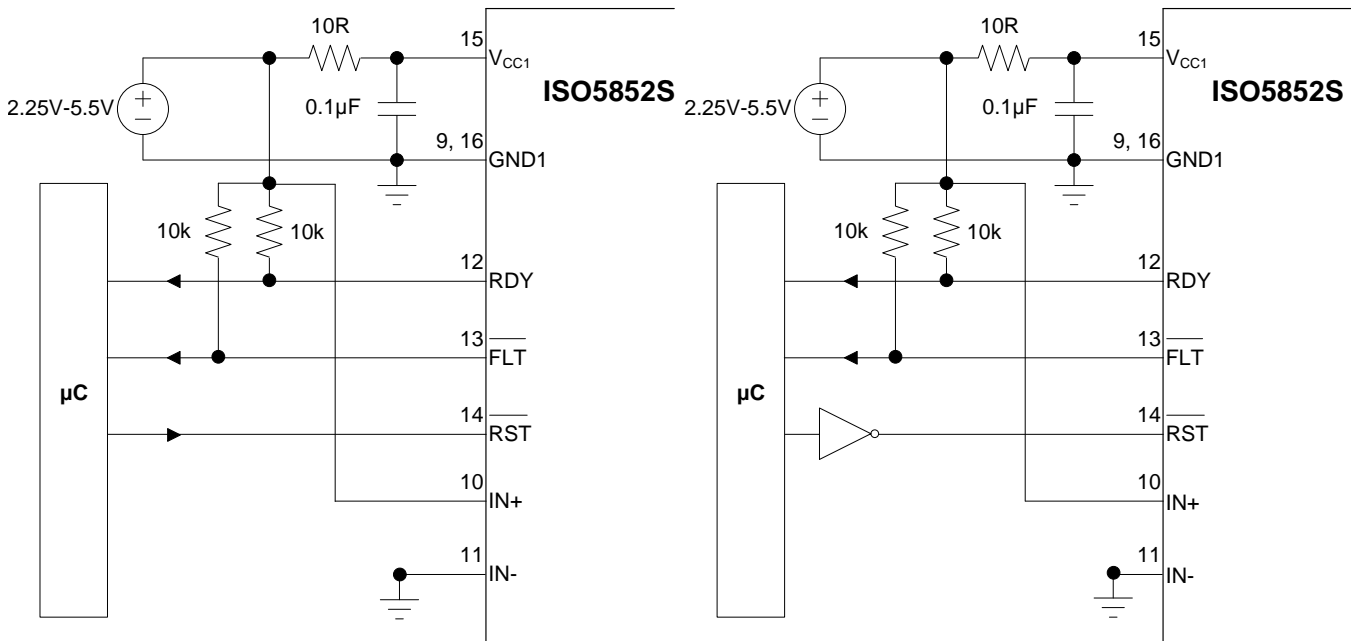


Figure 53. Auto Reset for Non-inverting and Inverting Input Configuration

10.2.2.7 DESAT Pin Protection

Switching inductive loads causes large instantaneous forward voltage transients across the freewheeling diodes of IGBTs. These transients result in large negative voltage spikes on the DESAT pin which draw substantial current out of the device. To limit this current below damaging levels, a 100-Ω to 1-kΩ resistor is connected in series with the DESAT diode.

Further protection is possible through an optional Schottky diode, whose low forward voltage assures clamping of the DESAT input to GND2 potential at low voltage levels.

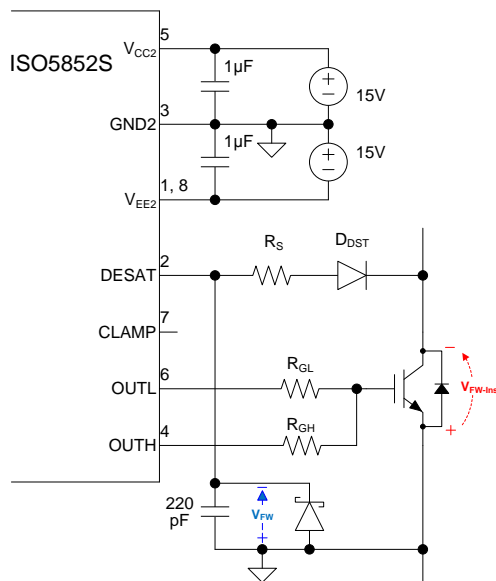


Figure 54. DESAT Pin Protection with Series Resistor and Schottky Diode

10.2.2.8 DESAT Diode and DESAT Threshold

The DESAT diode's function is to conduct forward current, allowing sensing of the IGBT's saturated collector-to-emitter voltage, $V_{(DESAT)}$, (when the IGBT is "on") and to block high voltages (when the IGBT is "off"). During the short transition time when the IGBT is switching, there is commonly a high dV_{CE}/dt voltage ramp rate across the IGBT. This results in a charging current $I_{(CHARGE)} = C_{(D-DESAT)} \times dV_{CE}/dt$, charging the blanking capacitor. $C_{(D-DESAT)}$ is the diode capacitance at DESAT.

To minimize this current and avoid false DESAT triggering, fast switching diodes with low capacitance are recommended. As the diode capacitance builds a voltage divider with the blanking capacitor, large collector voltage transients appear at DESAT attenuated by the ratio of $1 + C_{(BLANK)} / C_{(D-DESAT)}$.

Because the sum of the DESAT diode forward-voltage and the IGBT collector-emitter voltage make up the voltage at the DESAT-pin, $V_F + V_{CE} = V_{(DESAT)}$, the V_{CE} level, which triggers a fault condition, can be modified by adding multiple DESAT diodes in series: $V_{CE-FAULT(TH)} = 9\text{ V} - n \times V_F$ (where n is the number of DESAT diodes).

When using two diodes instead of one, diodes with half the required maximum reverse-voltage rating may be chosen.

10.2.2.9 Determining the Maximum Available, Dynamic Output Power, P_{OD-max}

The ISO5852S maximum allowed total power consumption of $P_D = 251\text{ mW}$ consists of the total input power, P_{ID} , the total output power, P_{OD} , and the output power under load, P_{OL} :

$$P_D = P_{ID} + P_{OD} + P_{OL} \quad (1)$$

With:

$$P_{ID} = V_{CC1-max} \times I_{CC1-max} = 5.5\text{ V} \times 4.5\text{ mA} = 24.75\text{ mW} \quad (2)$$

and:

$$P_{OD} = (V_{CC2} - V_{EE2}) \times I_{CC2-max} = (15\text{ V} - (-8\text{ V})) \times 6\text{ mA} = 138\text{ mW} \quad (3)$$

then:

$$P_{OL} = P_D - P_{ID} - P_{OD} = 251\text{ mW} - 24.75\text{ mW} - 138\text{ mW} = 88.25\text{ mW} \quad (4)$$

In comparison to P_{OL} , the actual dynamic output power under worst case condition, P_{OL-WC} , depends on a variety of parameters:

$$P_{OL-WC} = 0.5 \times f_{INP} \times Q_G \times (V_{CC2} - V_{EE2}) \times \left(\frac{r_{on-max}}{r_{on-max} + R_G} + \frac{r_{off-max}}{r_{off-max} + R_G} \right)$$

where

- f_{INP} = signal frequency at the control input IN+
 - Q_G = power device gate charge
 - V_{CC2} = positive output supply with respect to GND2
 - V_{EE2} = negative output supply with respect to GND2
 - r_{on-max} = worst case output resistance in the on-state: 4Ω
 - $r_{off-max}$ = worst case output resistance in the off-state: 2.5Ω
 - R_G = gate resistor
- (5)

Once R_G is determined, Equation 5 is to be used to verify whether $P_{OL-WC} < P_{OL}$. Figure 55 shows a simplified output stage model for calculating P_{OL-WC} .

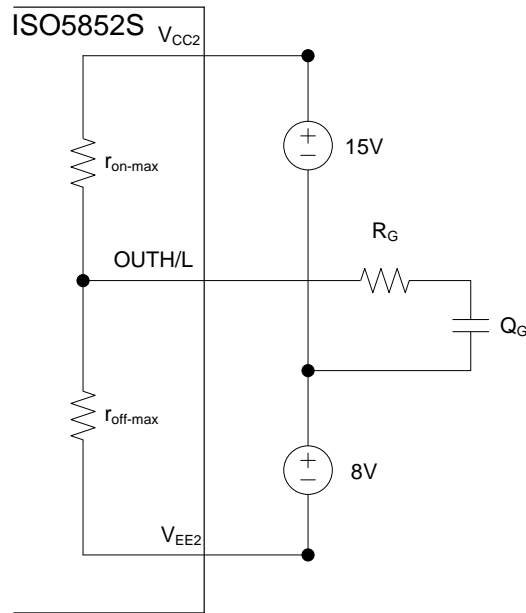


Figure 55. Simplified Output Model for Calculating P_{OL-WC}

10.2.2.10 Example

This examples considers an IGBT drive with the following parameters:

$$I_{ON-PK} = 2 \text{ A}, Q_G = 650 \text{ nC}, f_{INP} = 20 \text{ kHz}, V_{CC2} = 15 \text{ V}, V_{EE2} = -8 \text{ V} \quad (6)$$

Applying the value of the gate resistor $R_G = 10 \text{ } \Omega$.

Then, calculating the worst-case output power consumption as a function of R_G , using Equation 5 r_{on-max} = worst case output resistance in the on-state: $4 \text{ } \Omega$, $r_{off-max}$ = worst case output resistance in the off-state: $2.5 \text{ } \Omega$, R_G = gate resistor yields

$$P_{OL-WC} = 0.5 \times 20 \text{ kHz} \times 650 \text{ nC} \times (15 \text{ V} - (-8 \text{ V})) \times \left(\frac{4 \text{ } \Omega}{4 \text{ } \Omega + 10 \text{ } \Omega} + \frac{2.5 \text{ } \Omega}{2.5 \text{ } \Omega + 10 \text{ } \Omega} \right) = 72.61 \text{ mW} \quad (7)$$

Because $P_{OL-WC} = 72.61 \text{ mW}$ is below the calculated maximum of $P_{OL} = 88.25 \text{ mW}$, the resistor value of $R_G = 10 \text{ } \Omega$ is suitable for this application.

10.2.2.11 Higher Output Current Using an External Current Buffer

To increase the IGBT gate drive current, a non-inverting current buffer (such as the npn/pnp buffer shown in Figure 56) may be used. Inverting types are not compatible with the desaturation fault protection circuitry and must be avoided. The MJD44H11/MJD45H11 pair is appropriate for currents up to 8 A, the D44VH10/ D45VH10 pair for up to 15 A maximum.

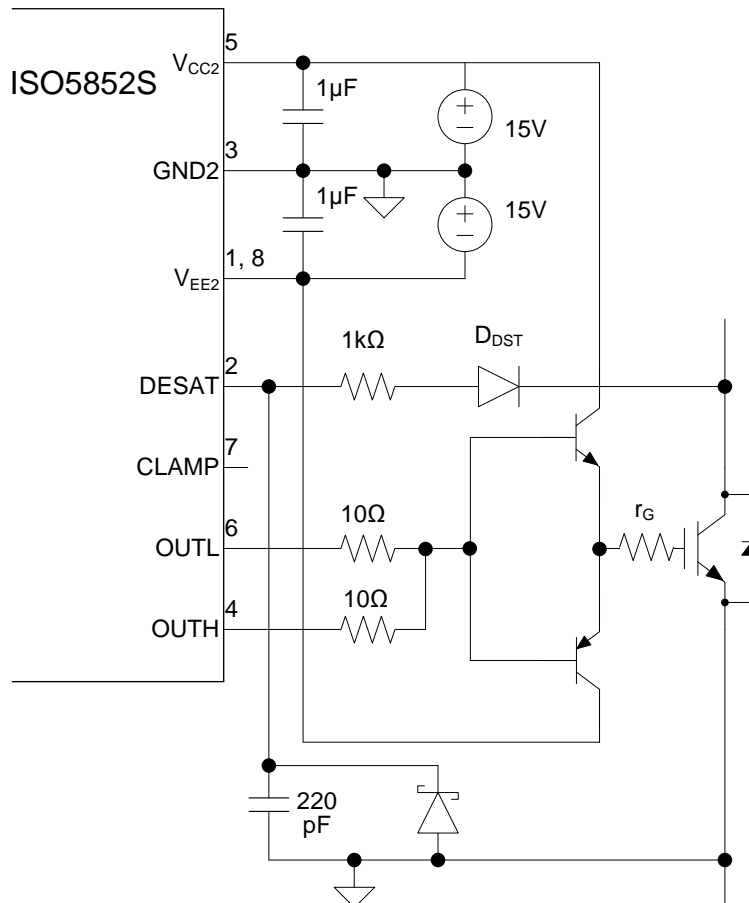
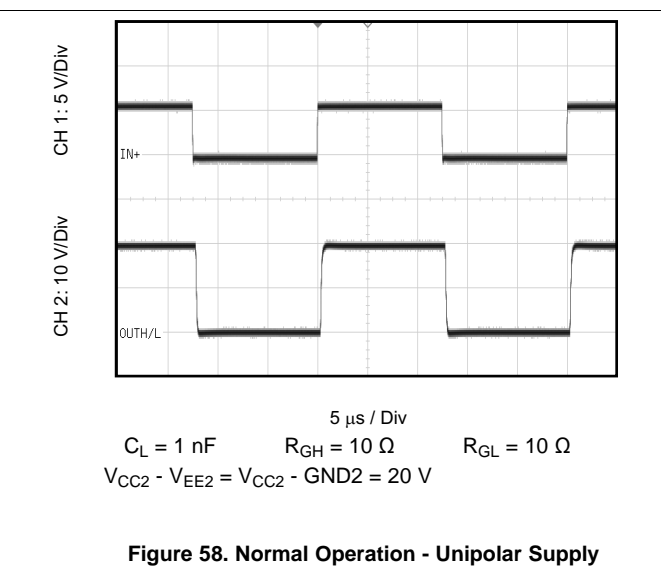
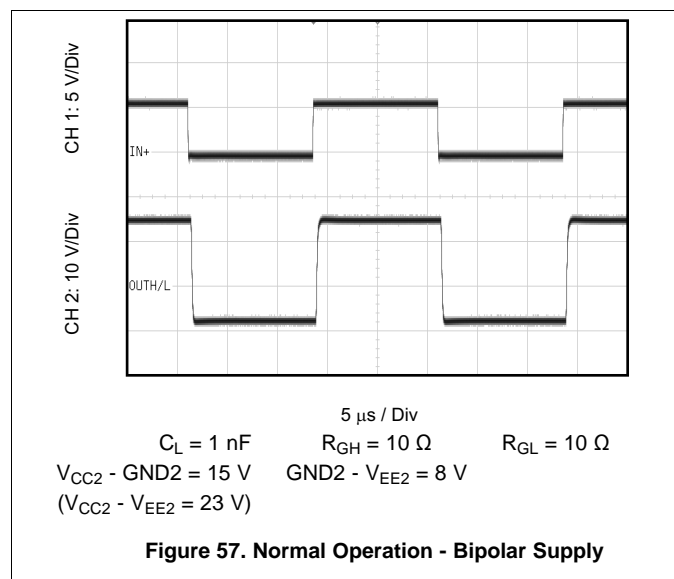


Figure 56. Current Buffer for Increased Drive Current

10.2.3 Application Curve



11 Power Supply Recommendations

To ensure reliable operation at all data rates and supply voltages, a 0.1- μF bypass capacitor is recommended at input supply pin V_{CC1} and 1- μF bypass capacitor is recommended at output supply pin V_{CC2} . The capacitors should be placed as close to the supply pins as possible. Recommended placement of capacitors needs to be 2-mm maximum from input and output power supply pin (V_{CC1} and V_{CC2}).

12 Layout

12.1 Layout Guidelines

A minimum of four layers is required to accomplish a low EMI PCB design (see [Figure 59](#)). Layer stacking should be in the following order (top-to-bottom): high-current or sensitive signal layer, ground plane, power plane and low-frequency signal layer.

- Routing the high-current or sensitive traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the gate driver and the microcontroller and power transistors. Gate driver control input, Gate driver output OUTH/L and DESAT should be routed in the top layer.
- Placing a solid ground plane next to the sensitive signal layer provides an excellent low-inductance path for the return current flow. On the driver side, use GND2 as the ground plane.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100 pF/inch². On the gate-driver V_{EE2} and V_{CC2} can be used as power planes. They can share the same layer on the PCB as long as they are not connected together.
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.

For more detailed layout recommendations, including placement of capacitors, impact of vias, reference planes, routing etc. see Application Note [SLLA284](#), *Digital Isolator Design Guide*.

12.2 PCB Material

Standard FR-4 epoxy-glass is recommended as PCB material. FR-4 (Flame Retardant 4) meets the requirements of Underwriters Laboratories UL94-V0, and is preferred over cheaper alternatives due to its lower dielectric losses at high frequencies, less moisture absorption, greater strength and stiffness, and its self-extinguishing flammability-characteristics.

12.3 Layout Example

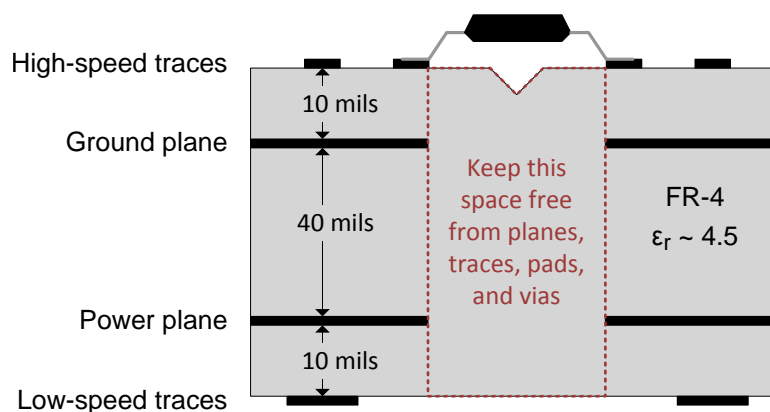


Figure 59. Recommended Layer Stack

13 Device and Documentation Support

13.1 Documentation Support

13.1.1 Related Documentation

For related documentation see the following:

- *ISO5852S Evaluation Module (EVM) User's Guide*, [SLLU207](#)
- *Digital Isolator Design Guide*, [SLLA284](#)
- *Isolation Glossary* ([SLLA353](#))

13.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

13.3 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

13.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

13.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ISO5852SDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-250C-1 YEAR	-40 to 125	ISO5852S	Samples
ISO5852SDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	ISO5852S	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

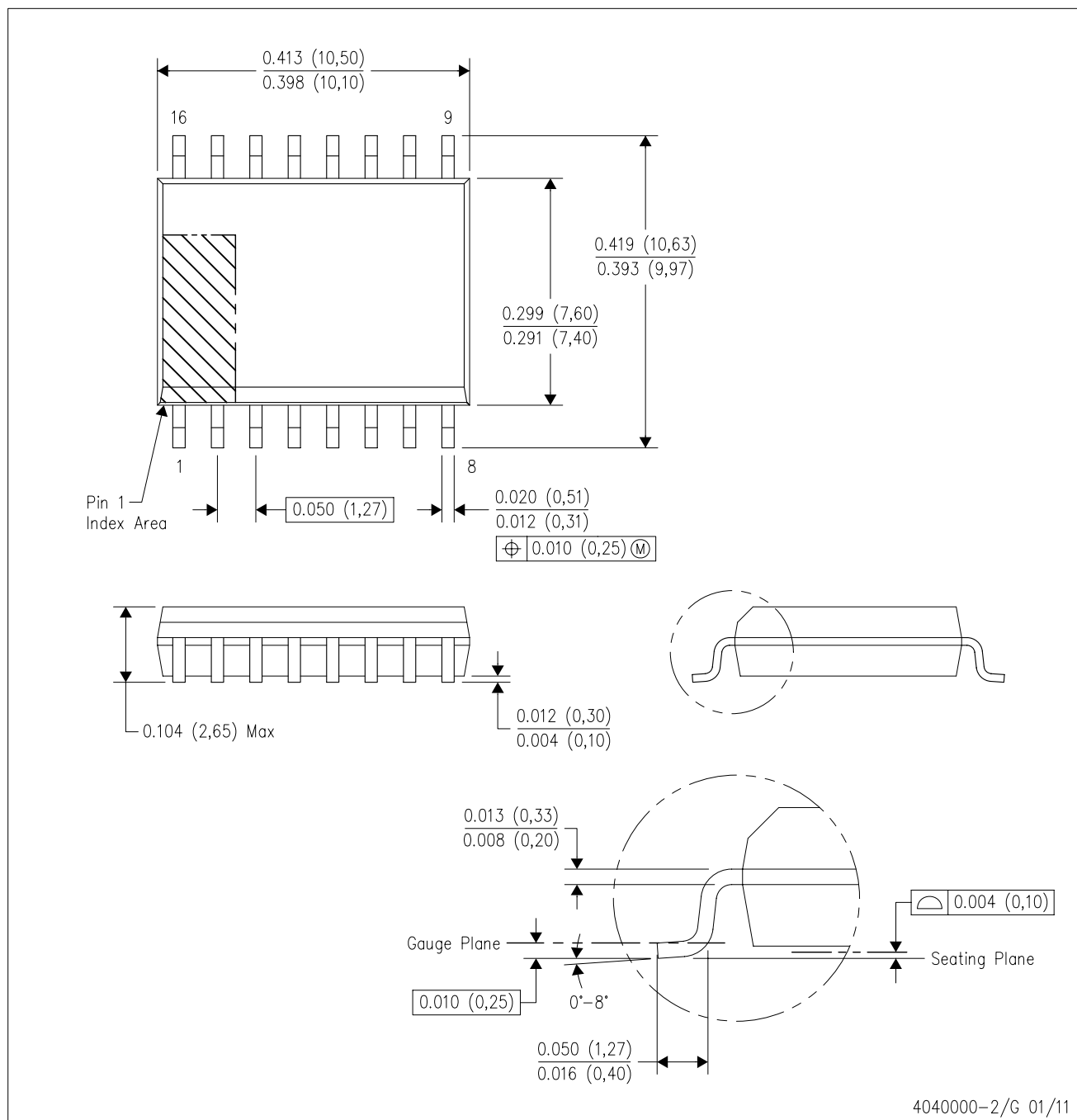
(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

DW (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS-013 variation AA.

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have **not** been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products

Audio	www.ti.com/audio
Amplifiers	amplifier.ti.com
Data Converters	dataconverter.ti.com
DLP® Products	www.dlp.com
DSP	dsp.ti.com
Clocks and Timers	www.ti.com/clocks
Interface	interface.ti.com
Logic	logic.ti.com
Power Mgmt	power.ti.com
Microcontrollers	microcontroller.ti.com
RFID	www.ti-rfid.com
OMAP Applications Processors	www.ti.com/omap
Wireless Connectivity	www.ti.com/wirelessconnectivity

Applications

Automotive and Transportation	www.ti.com/automotive
Communications and Telecom	www.ti.com/communications
Computers and Peripherals	www.ti.com/computers
Consumer Electronics	www.ti.com/consumer-apps
Energy and Lighting	www.ti.com/energy
Industrial	www.ti.com/industrial
Medical	www.ti.com/medical
Security	www.ti.com/security
Space, Avionics and Defense	www.ti.com/space-avionics-defense
Video and Imaging	www.ti.com/video

TI E2E Community

e2e.ti.com